



# Development of MALTA, a radiation hard high-speed monolithic CMOS sensor for the ATLAS experiment at the HL-LHC

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On behalf of

The MALTA team

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- Introduction to MAPS in HEP
- MALTA
  - Tower Jazz 180 nm Modified Process
  - One of 2 chips based on Investigator targeting ATLAS
  - 2018 SPS test beam results
  - Motivation for miniMALTA
- MiniMALTA
  - Re-designed substrate, front-end
  - 2019 test beam results
  - TID measurements
- MALTA SC, MALTA V2 and the future

- Why Monolithic Active Pixel Sensors (MAPS):
  - Easier detector assembly
  - Low material budget
  - Potentially smaller feature sizes, capacitances
  - CMOS is industry standard – large firms, high throughput, low cost
- MAPS in HEP:
  - Main challenge is designing radiation tolerant devices
    - Typically collect charge via diffusion, but need depletion to go above  $1e13 n_{eq}/cm^2$
    - For ATLAS ITk L4:  **$1.5e15 n_{eq}/cm^2$ , 100 MRad**
    - Solution: reverse biased, thin epitaxial depletion region
    - Called “DMAPS” for “depleted MAPS”
  - ALPIDE chip from TJ 180 nm to be installed during ALICE tracker upgrade
  - Prototypes from LFoundry 150 nm, AMS 180 nm, and Tower Jazz 180 nm (TJ) designed for ATLAS radiation specifications
  - **This talk focuses on one of two TJ 180 nm chips for ATLAS, the MALTA**

# DMAPS in HEP



2 types of design proposed for implementing DMAPS in HEP:

Large Fill-factor

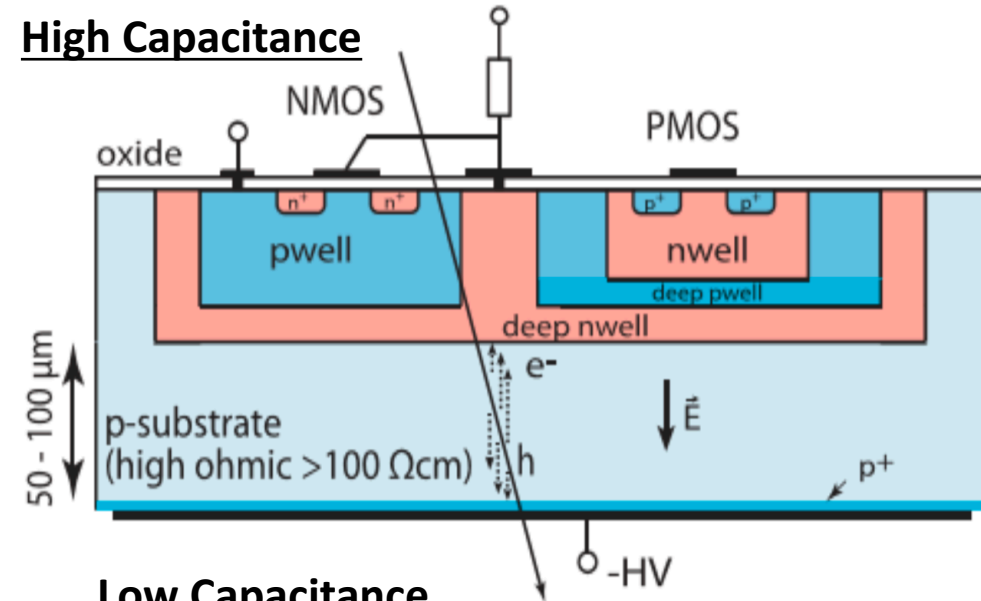
- Electronics in collection n-well
- High resistivity substrate
- Large signal
- Larger fill factor
- **High capacitance (~100 fF)**

Small Fill-factor

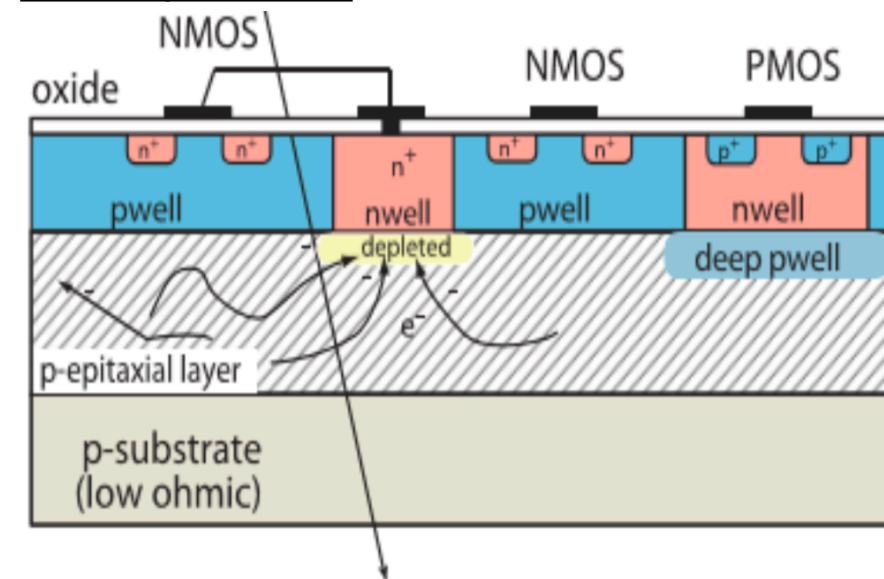
- Electronics next to electrodes
- Low resistivity substrate
- Epitaxial layer for collection
- Smaller fill factor
- Weak field long collection times away from the electrode
- **Low capacitance (~5 fF)**
- Design of ALPIDE, MALTA

$$\text{Depletion depth} \sim \sqrt{V\rho}$$

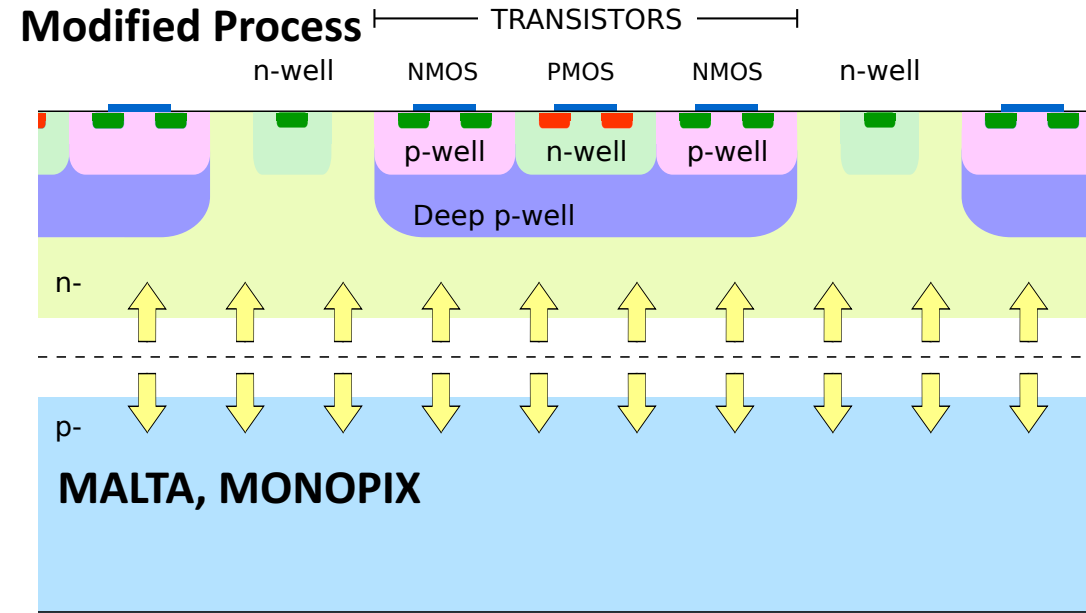
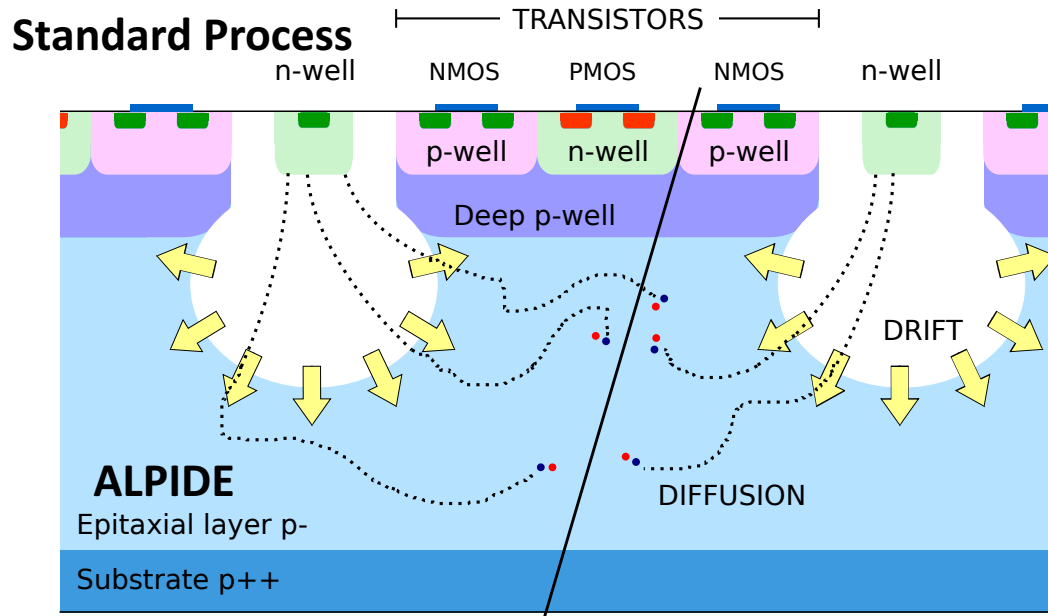
## High Capacitance



## Low Capacitance



# Modified TJ 180 nm Process



- 25 -30  $\mu\text{m}$  epitaxial layer
- Small collection electrode,  $\sim 5$  fF input capacitance
- Modified process with uniform n-implant to improve lateral depletion
  - Periphery efficiency, time walk
- 2 chips: MALTA (asynchronous) and MONOPIX (synchronous)
- MALTA based on the ALPIDE chip in ALICE
- Produced Jan 2018

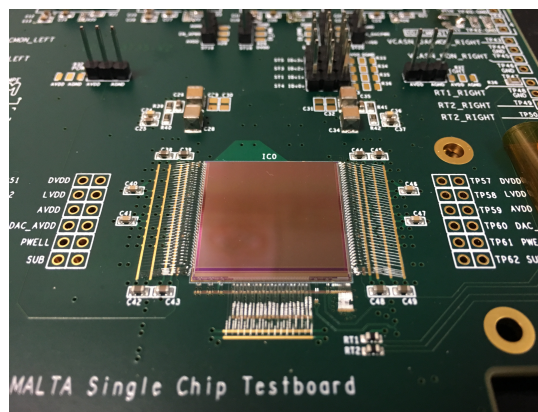
W. Snoeys et al. DOI 10.1016/j.nima.2017.07.046  
H. Pernegger et al 2017 JINST 12 P06008

# TJ 180 nm MALTA for ATLAS

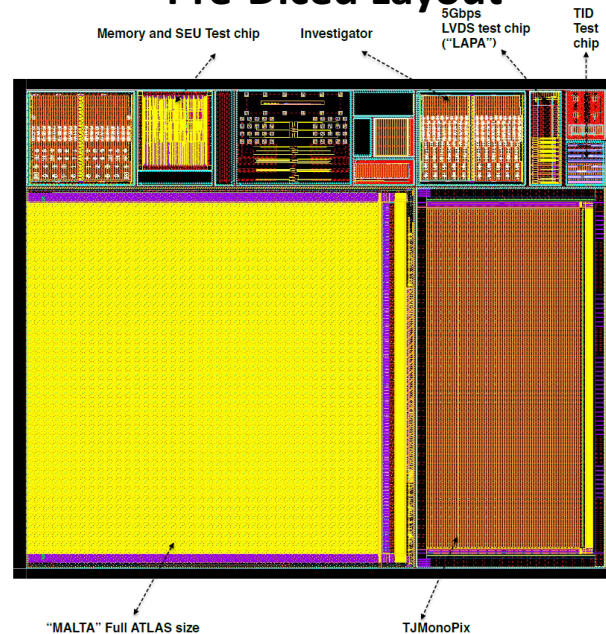


- 20 x 22 mm
- 512 x 512 pixel matrix
- 36.4  $\mu\text{m}$  pixels with CSA + discriminator + flip-flop
- 3  $\mu\text{m}$  electrode with capacitance < 5 fF
- Novel asynchronous readout architecture for high hit rate capability with 40bit parallel data bus for streaming
- 5 Gbit/s readout
- Low analog power (< 70 mW/cm<sup>2</sup>)

Chip bonded on Testboard



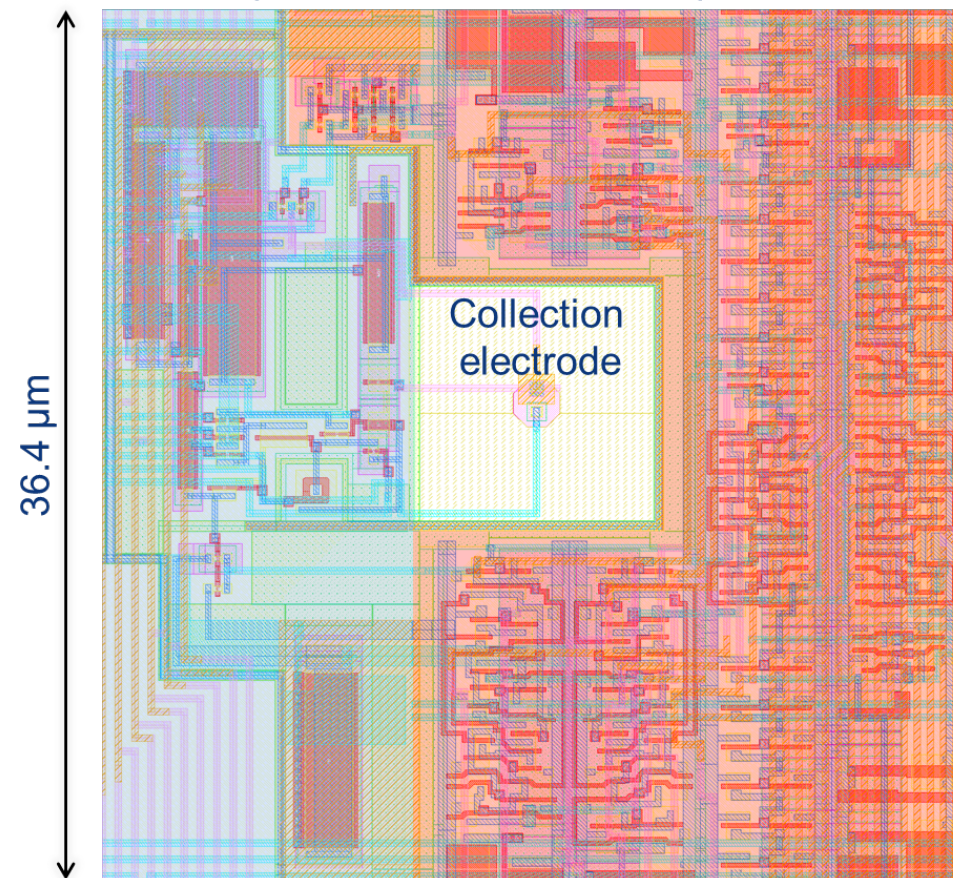
Pre-Diced Layout



Pixel Schematic

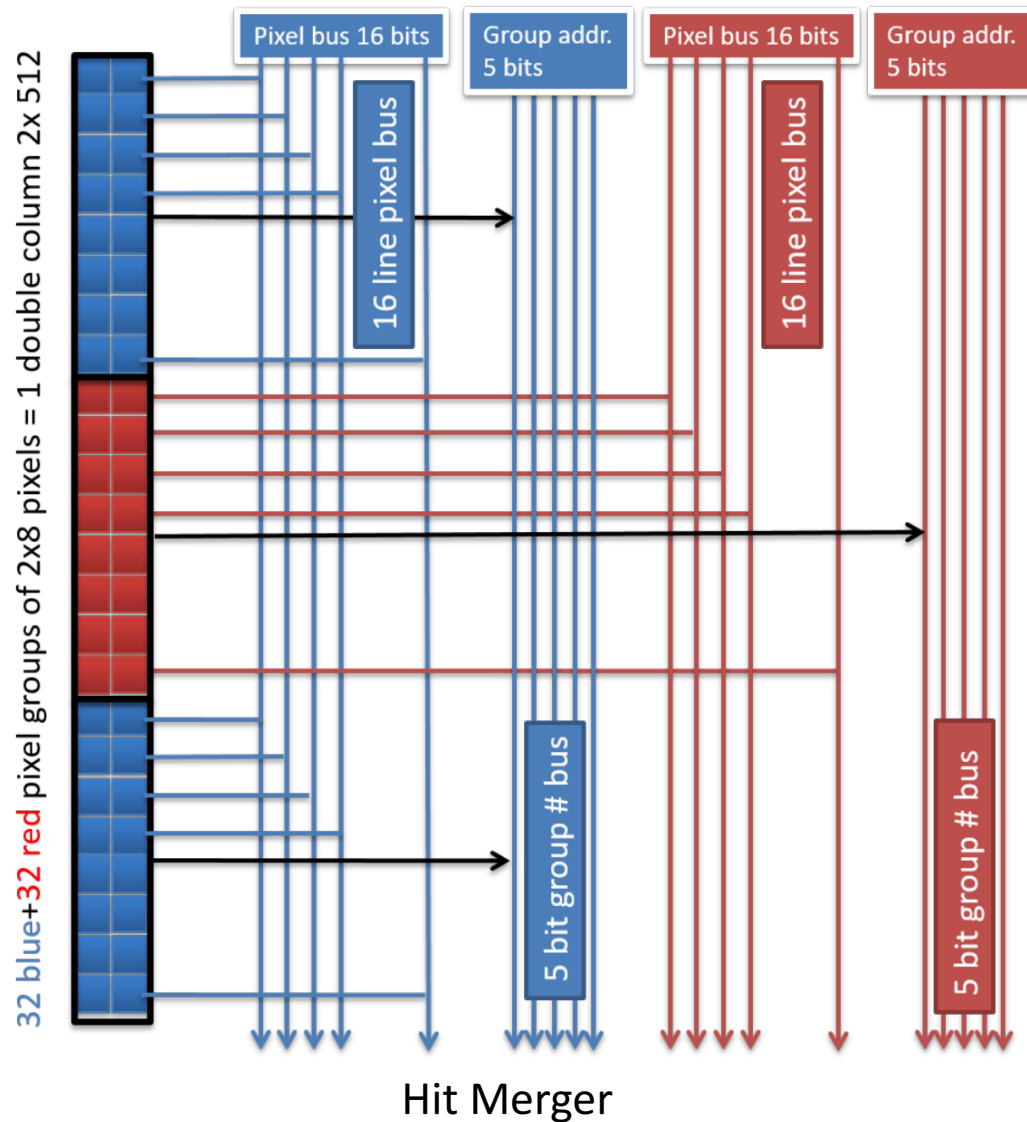
Analog

Digital



36.4  $\mu\text{m}$

# MALTA Readout architecture



- Asynchronous readout
- No clock distributed to matrix (low power)
- Hit readout from discriminator immediately (fast)
- Double column structure
- Alternating “red” & “blue” groups of 2 x 8 pixels
- 16-bit bus shared groups of same color
- 5 bits for group ID
- Hits merged at periphery, timing information included
- Each hit is written as 40-bit word w/ timing (BCID), double column, color, group, and pixel encoded

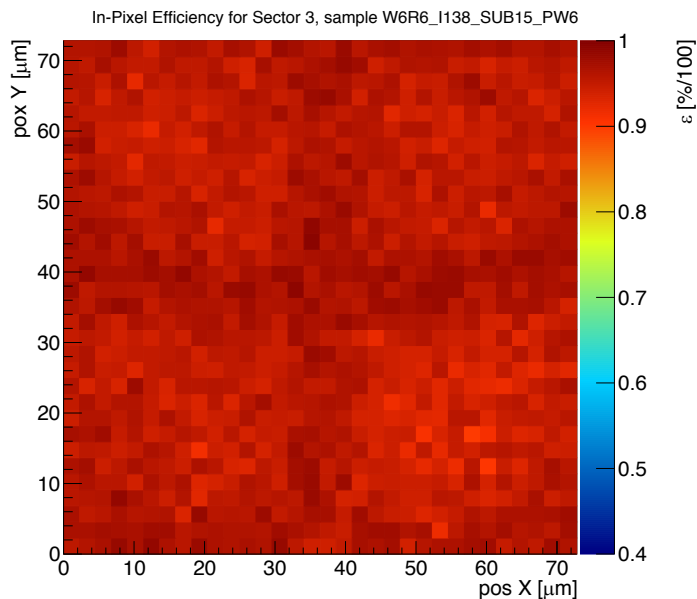
# Efficiency Results (2018)



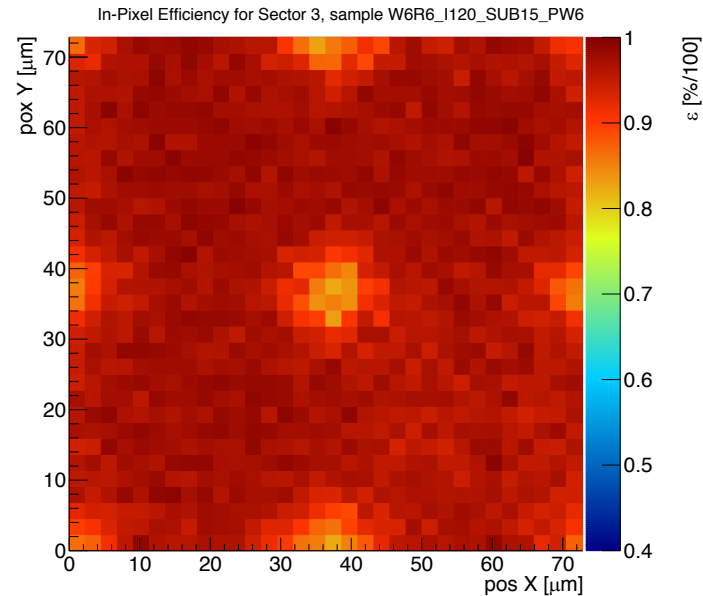
- 180 GeV pions at SPS at CERN, Summer 2018
- Results show decrease in efficiency after irradiation to  $5e14 \text{ n}_{\text{eq}}/\text{cm}^2$
- Inefficiency in pixel periphery
- Too noisy to operate at low threshold after irradiation
- 4 pixels per plot

## Unirradiated

Threshold  $\sim 250 \text{ e}^-$

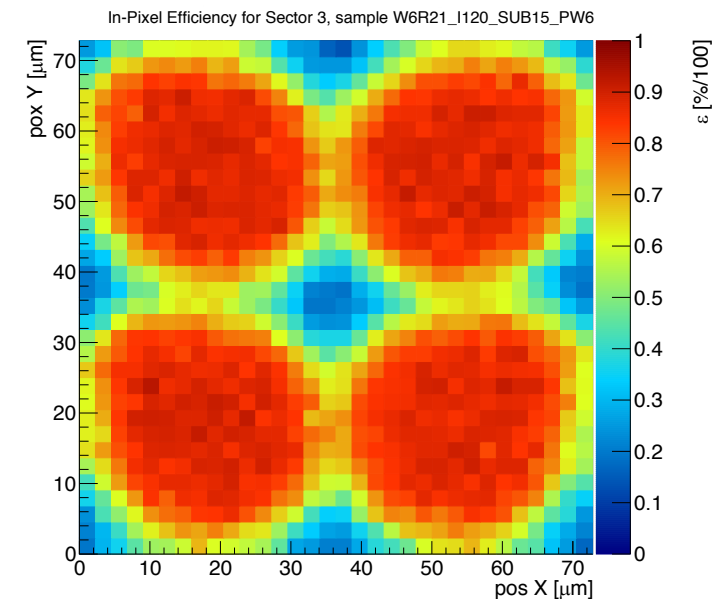


Threshold  $\sim 400 \text{ e}^-$



$5e14 \text{ n}_{\text{eq}}/\text{cm}^2$

Threshold  $\sim 400 \text{ e}^-$



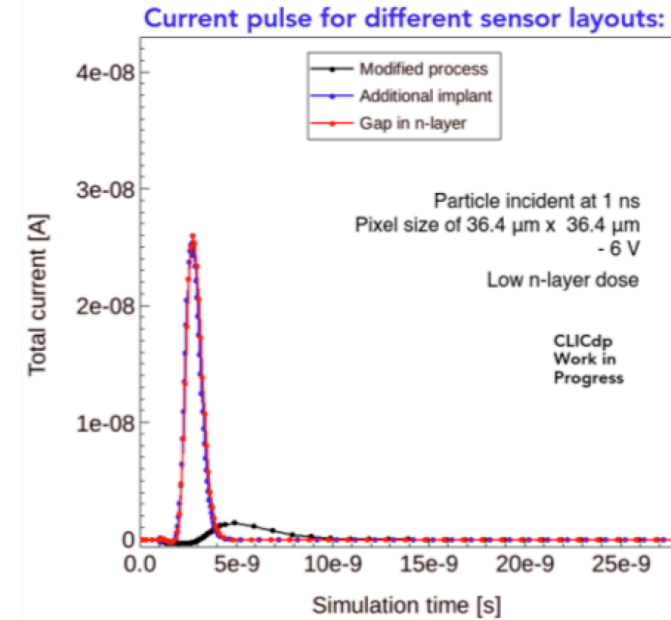
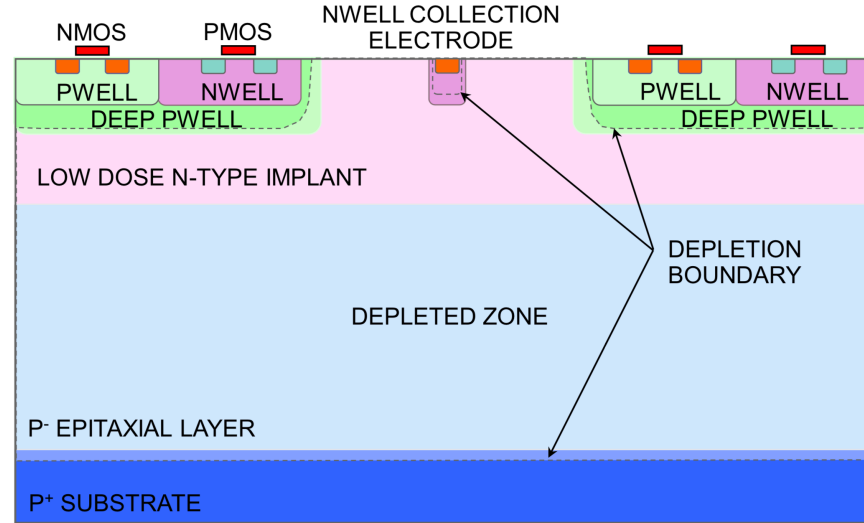


# Redesign: MiniMALTA Substrate

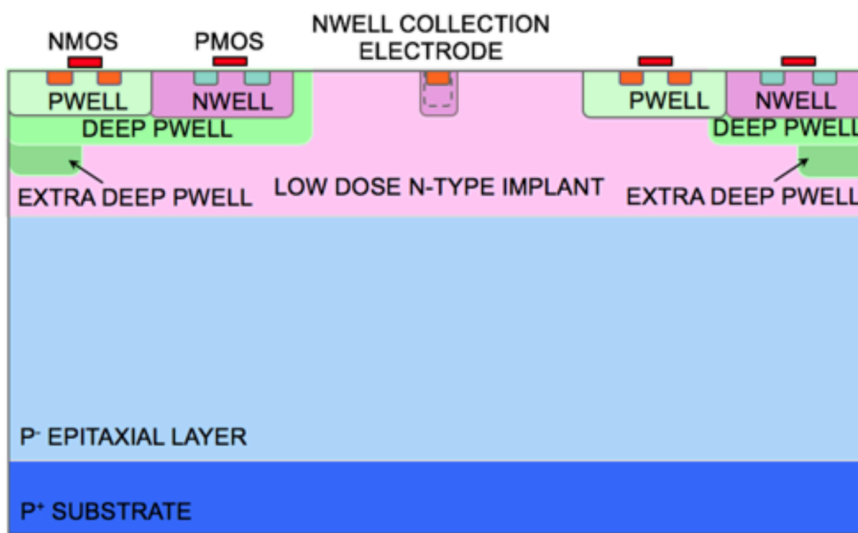


- 2 changes to sensor substrate to increase lateral field near electrode:
  - Extra deep p-well
  - Gap in n- layer
- Simulation predicts a faster, higher amplitude signal for hits in periphery
  - Before & after irradi

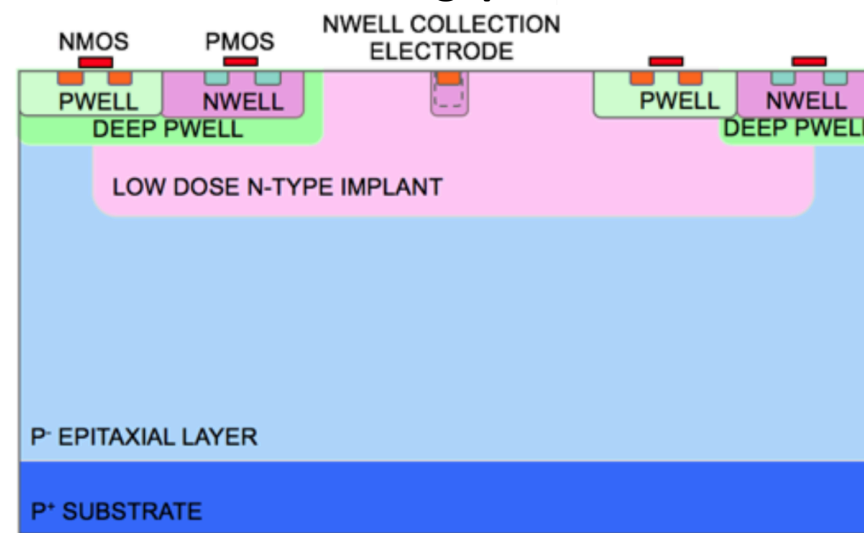
Continuous n- layer (old design)



Extra deep p-well



n- gap

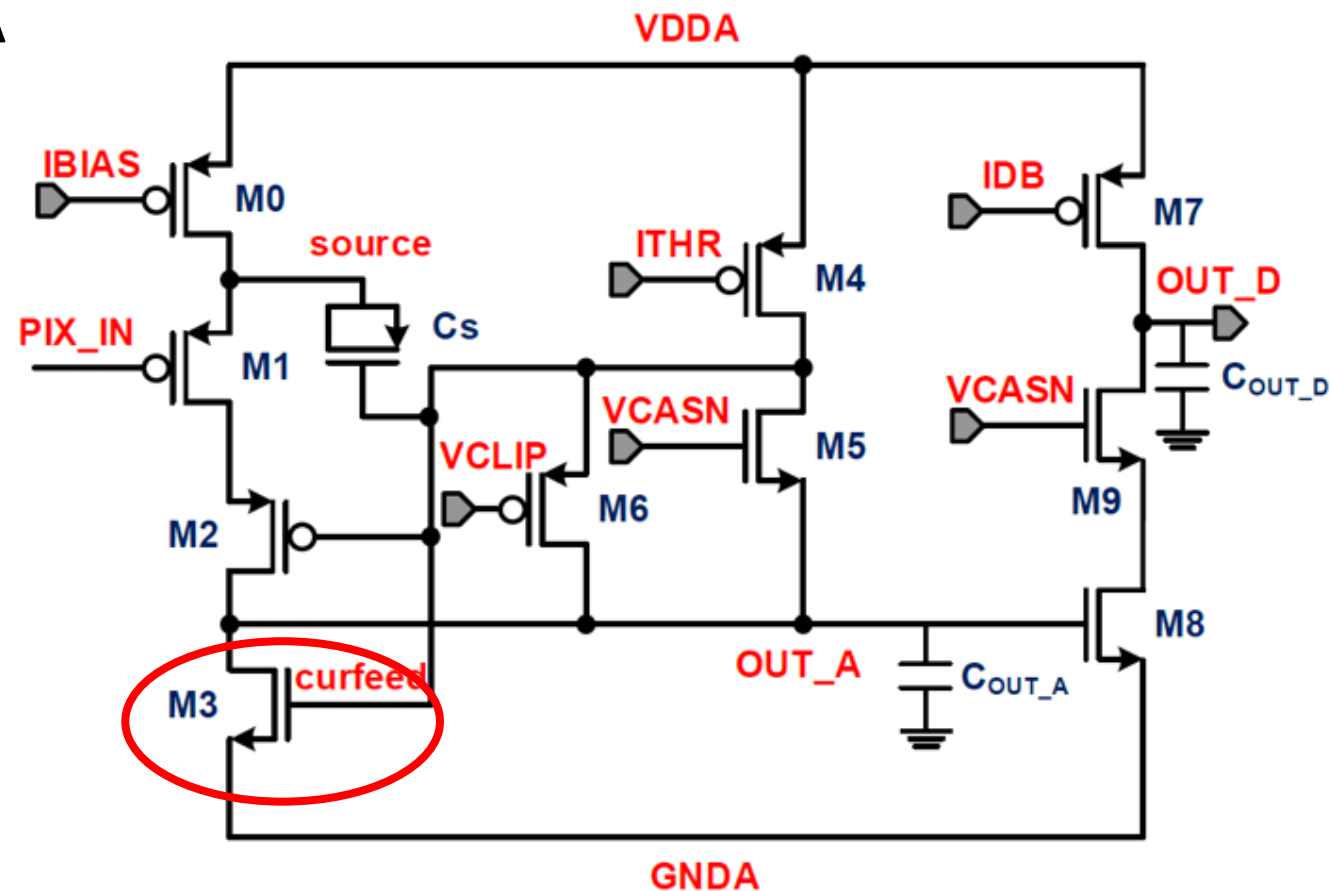


M. Munker et al. 9<sup>th</sup> Workshop on Semiconductor Pixel Detectors for Particles and Imaging (PIXEL), December 2018.

# Redesign: MiniMALTA Front End



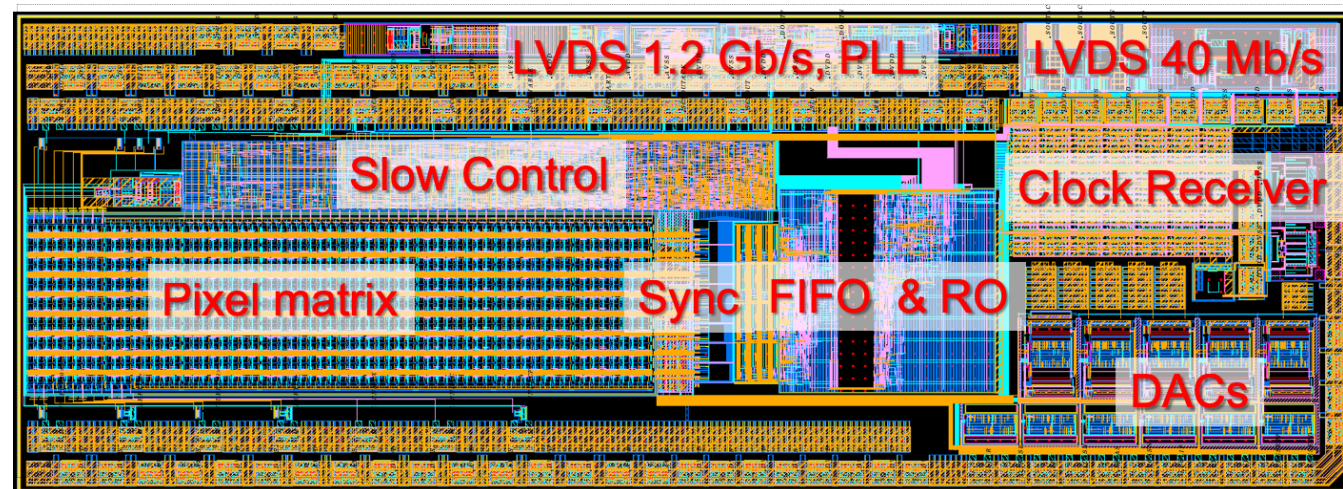
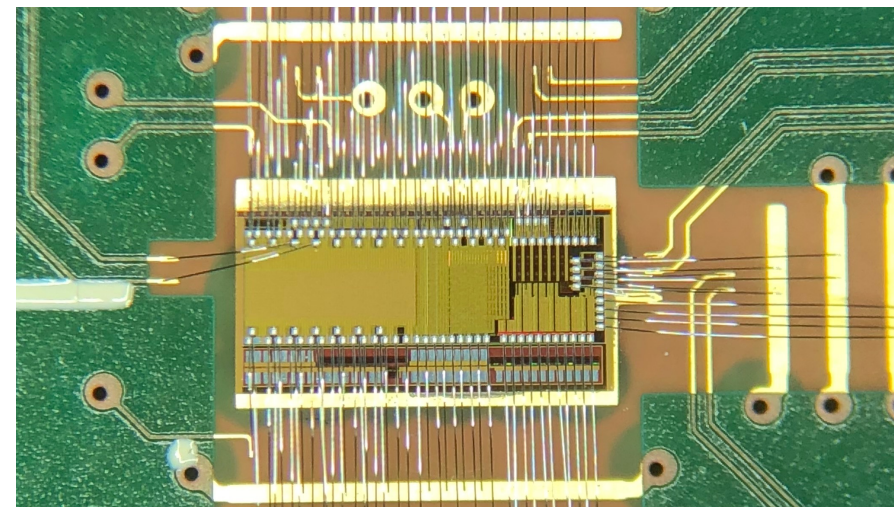
- Random Telegraph ('popcorn') noise prevented low thresholds in MALTA
- M3 NMOS transistor enlarged
- Gain increase
- Lower thresholds
- Better threshold dispersion
- Fewer noisy pixels



# MiniMALTA Chip



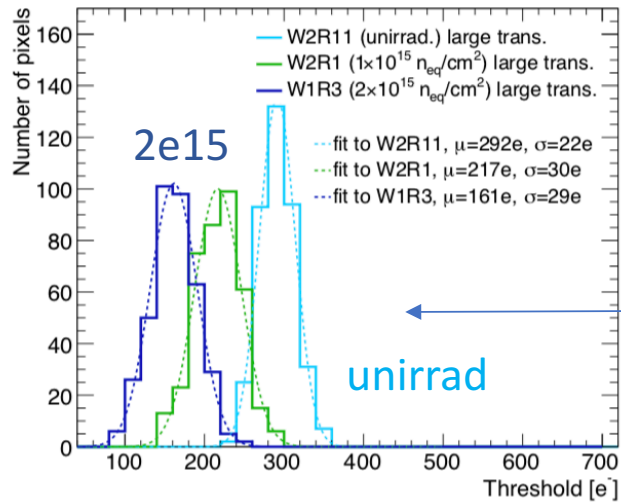
- Chip produced in Jan 2019
- 64 x 16 pixel matrix
- 36.4  $\mu\text{m}$  pitch
- 8 redesigned sectors
- 0.5 x 0.1 mm
- Lab measurements show front-end is improved w/ addition of large transistor



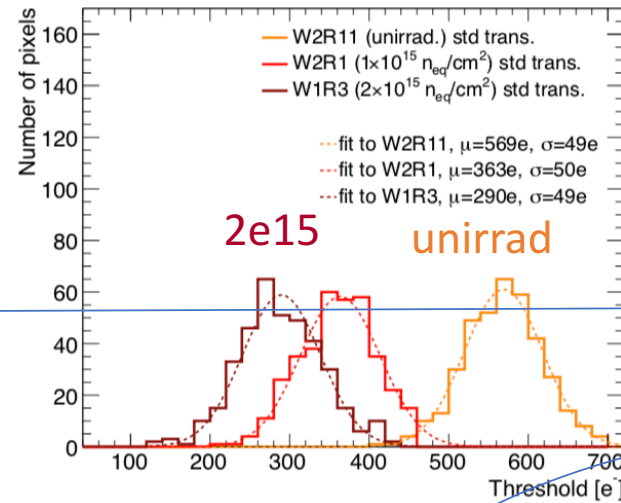
# MiniMALTA Threshold Scans



Enlarged Transistor Threshold



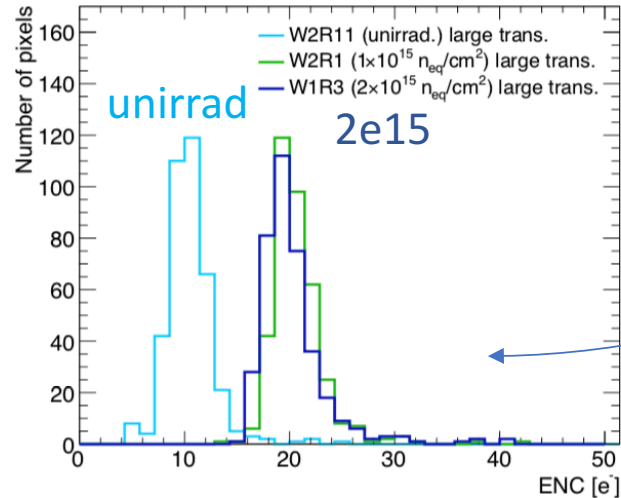
Standard Transistor Threshold



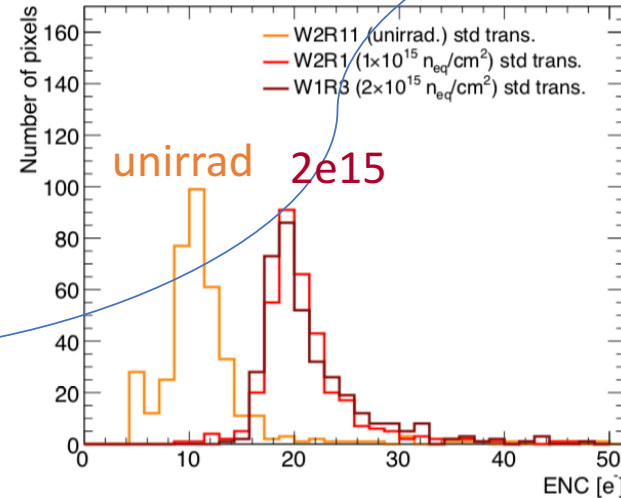
Threshold scans show:

- Improvement of front end with **enlarged transistor**
  - Lower thresholds
  - Lower noise
  - **Fewer high-noise pixels**

Enlarged Transistor Noise



Standard Transistor Noise

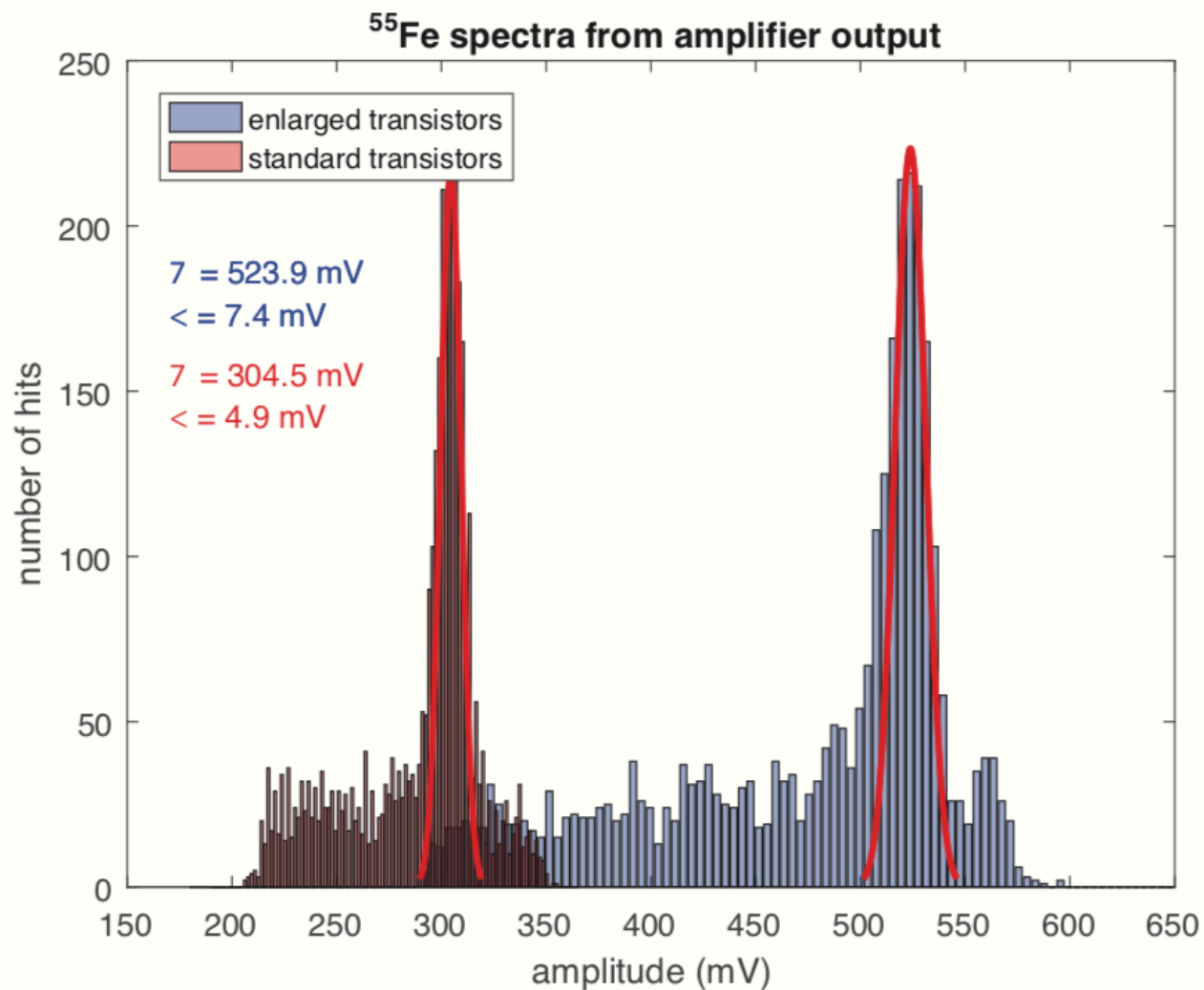


Irradiation dependence

- Lower thresholds
- Noise increases with irradiation, though plateaus at  $2e15 n_{eq}/cm^2$

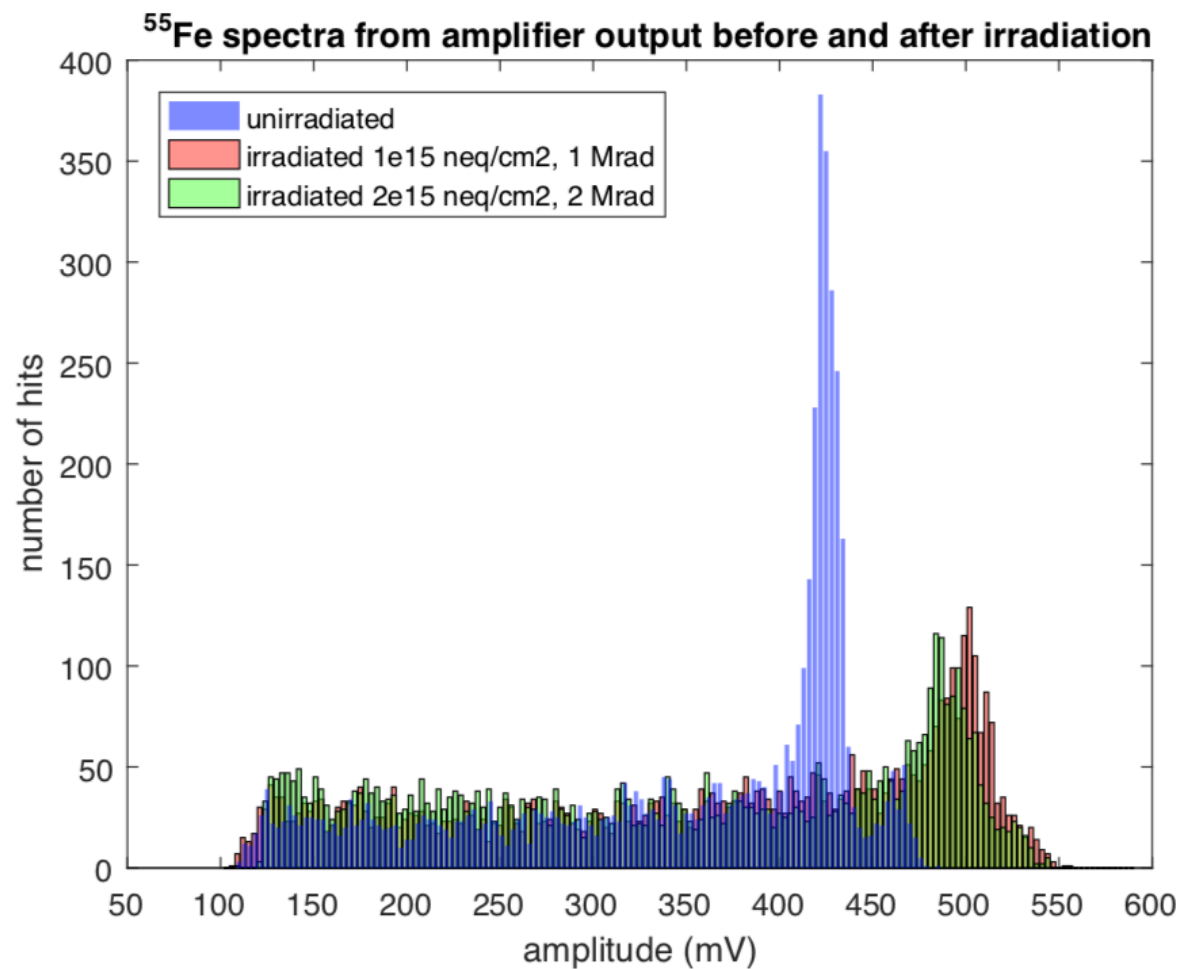
Submitted to arXiv:1909.11987v1

# MiniMALTA X-ray measurements



Submitted to arXiv:1909.11987v1

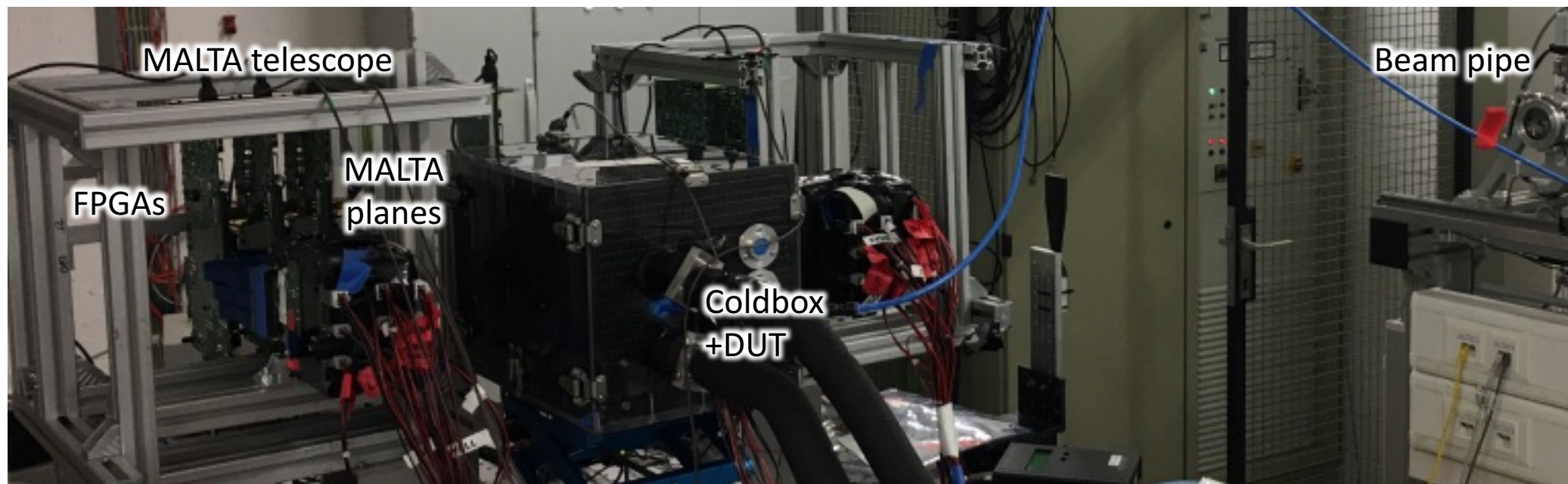
- Fe-55 gamma source
  - 5.9 keV X-rays => ~1600 e-
- Increased gain w/ enlarged transistor



Submitted to arXiv:1909.11987v1

- Fe-55 gamma source
  - 5.9 keV X-rays
- Measurement of unirradiated, 1e15  $n_{eq}/cm^2$ , and 2e15  $n_{eq}/cm^2$  samples
- Increase in gain after irradiation?
  - Front-end changes?
  - No: Measurements => Change in pixel capacitance
- Does improved performance lead to higher efficiency?

# MiniMALTA Efficiency



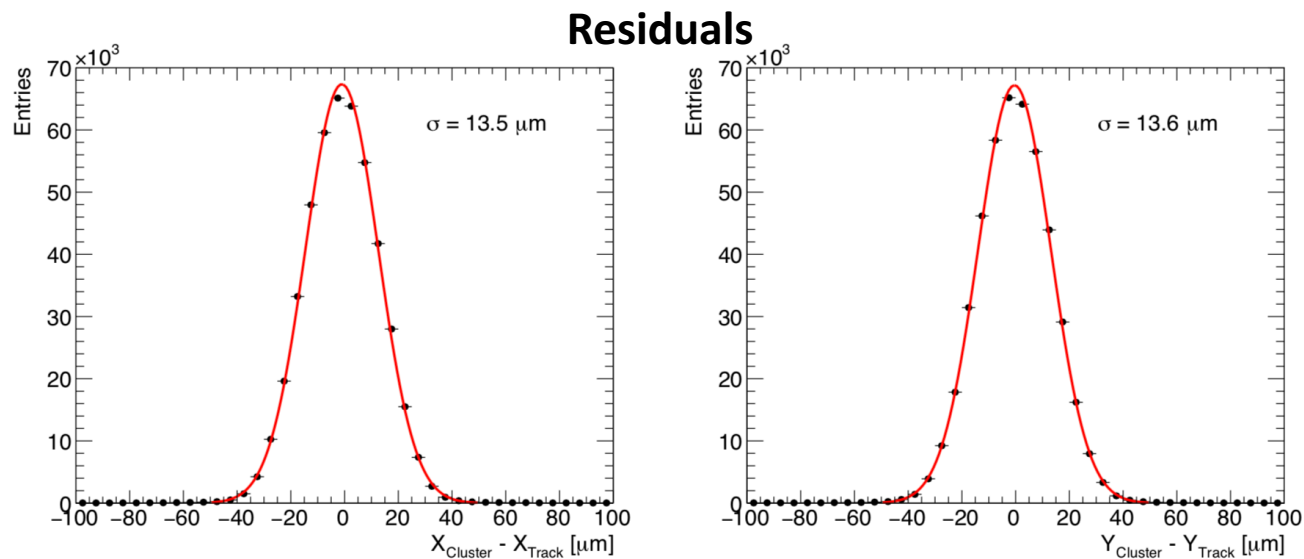
- April 2019 test beams at DESY and ELSA
- 2.5 - 5 GeV electron beams
- Beam telescopes to reconstruct tracks, measure efficiencies
  - MIMOSA at DESY, MALTA at ELSA
- Tested neutron irradiated MiniMALTA samples at  $1e15 n_{eq}/cm^2$

# MALTA Beam Telescope



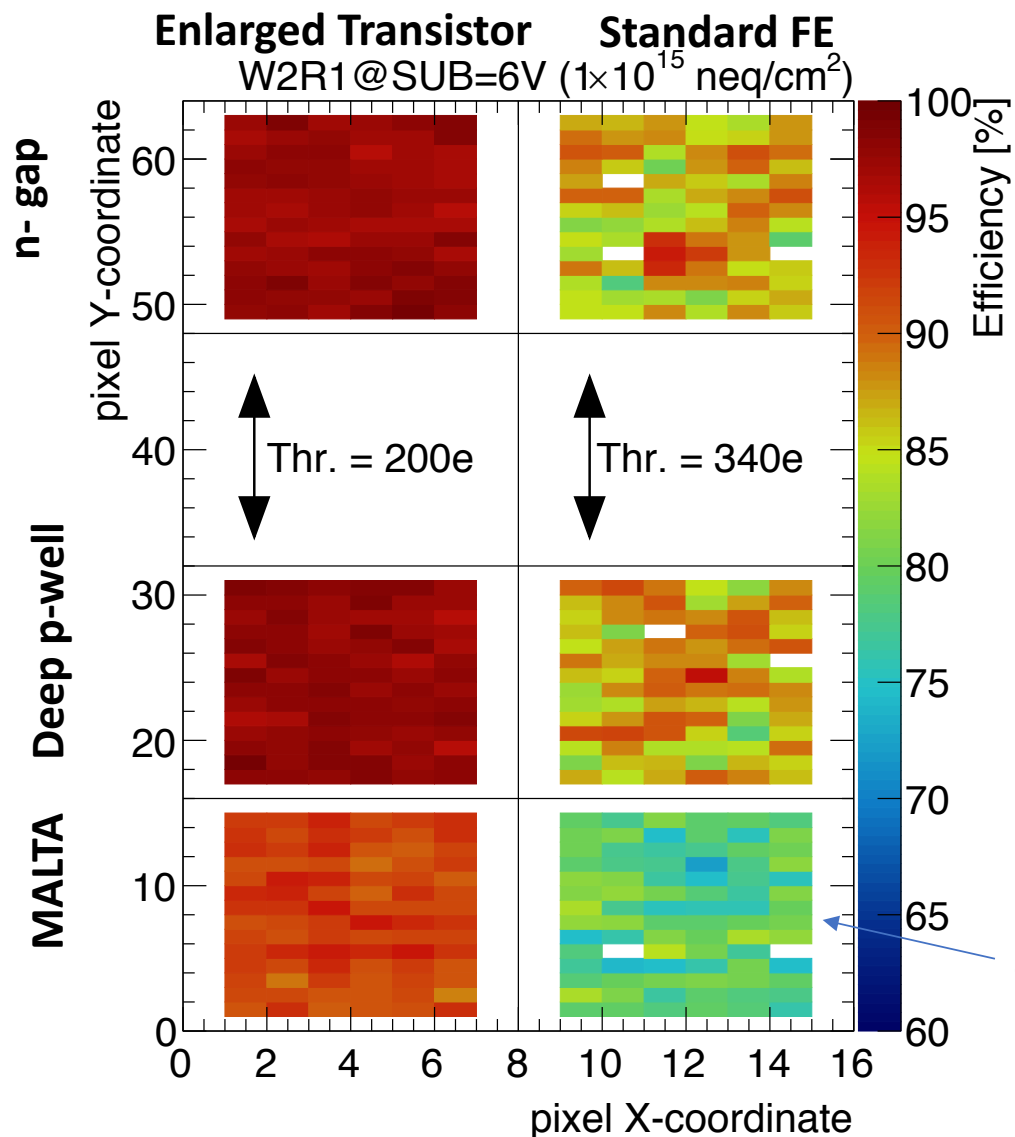
- Telescope constructed from 6 MALTA planes
- Xilinx Virtex-7 FPGA VC707 for readout
- Developed during SPS test beam, 2018
- Used at ELSA test beam in 2019, currently at DESY
- 13  $\mu\text{m}$  residuals with 3 GeV electrons at DESY
  - GBL in Proteus for tracking
  - Predict 6  $\mu\text{m}$  with 180 GeV pions
- Time resolution  $\sim 10$  ns
- Now includes custom TLU

MALTA Beam Telescope at SPS





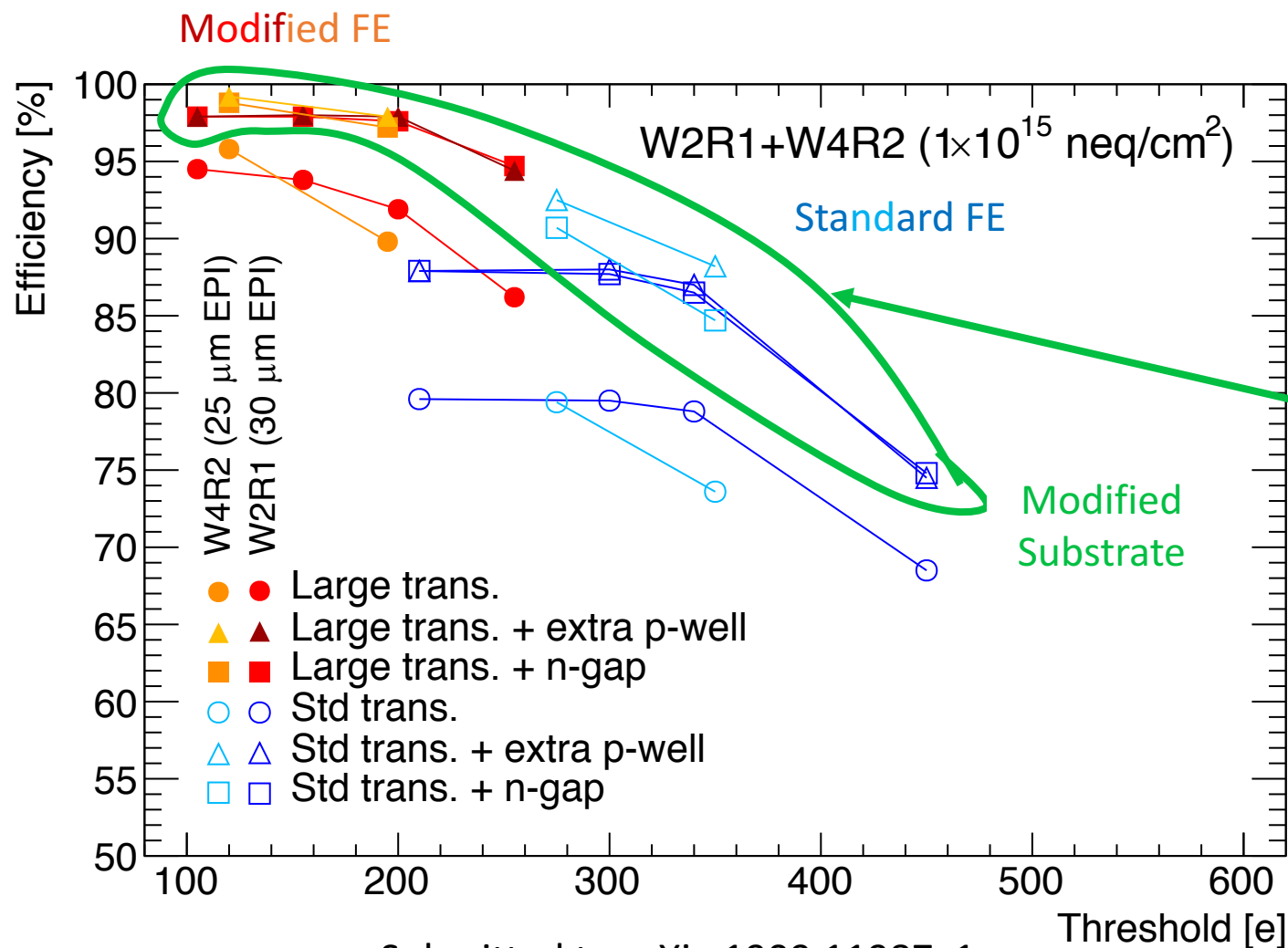
# MiniMALTA Efficiency $1e15 n_{eq}/cm^2$



- Re-designed sectors show much improvement
- No signal from PMOS reset sector
- Efficient to  $1e15 n_{eq}/cm^2$
- => Substrate **and** front-end changes are necessary
- Edges of regions limited by scattering, edge effects b/w matrices

Submitted to arXiv:1909.11987v1

# MiniMALTA Efficiency Results



## Summary of $1e15 n_{eq}/cm^2$ efficiencies

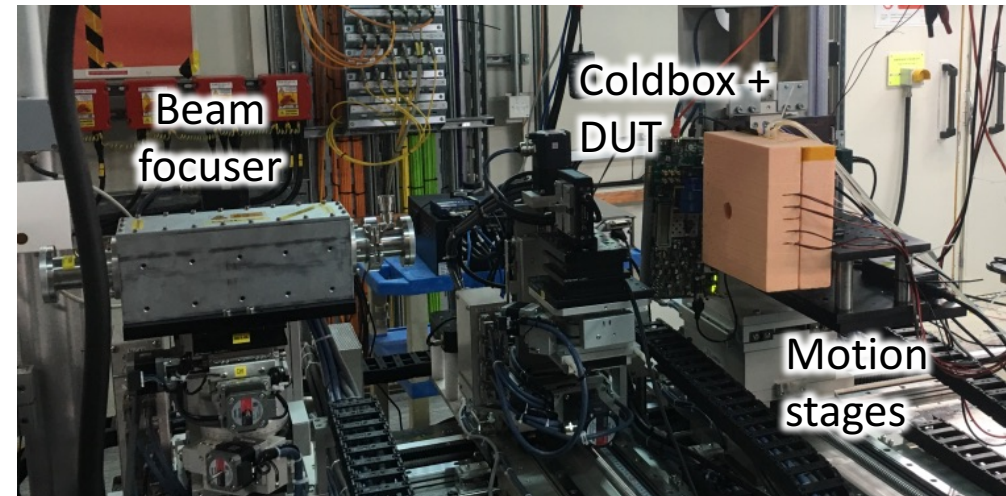
- One 25  $\mu m$  & one 30  $\mu m$
- [compare at const. threshold]
- Extra deep p-well and n-gap at higher efficiency than standard substrate
- **Modified** front-end, more efficient, lower thresholds than **Standard**
- Threshold lower for 30  $\mu m$  than 25  $\mu m$  epitaxial
- **Is loss of efficiency still in periphery?**
- **TID?**

# Diamond Test Beam



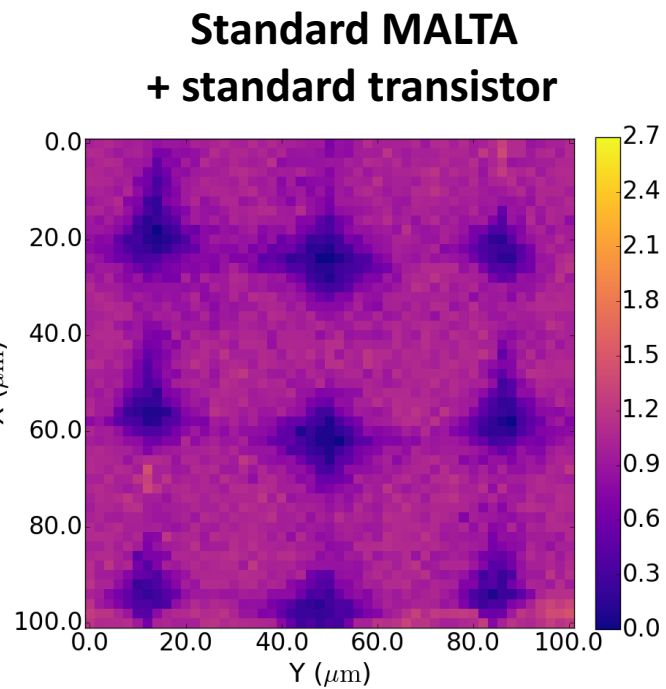
X-Ray test beam measurements at Diamond Light Source in April 2019

- 2  $\mu\text{m}$  beam spot scanned across pixels
- Pixel performance decreases with irradiation in MALTA sector
- New p-well and n-gap designs + enlarged transistor improve pixel performance
- Proton irradiated samples w/ TID +NIEL

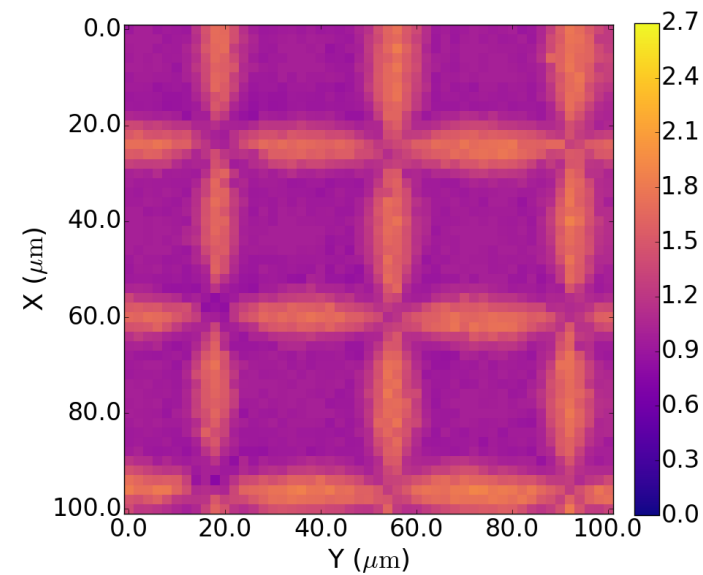


## Scaled Hit Maps ≠ efficiency

W2R1  
 $1e15 \text{ n}_{\text{eq}}/\text{cm}^2$   
(neutron irradiation)  $\times$



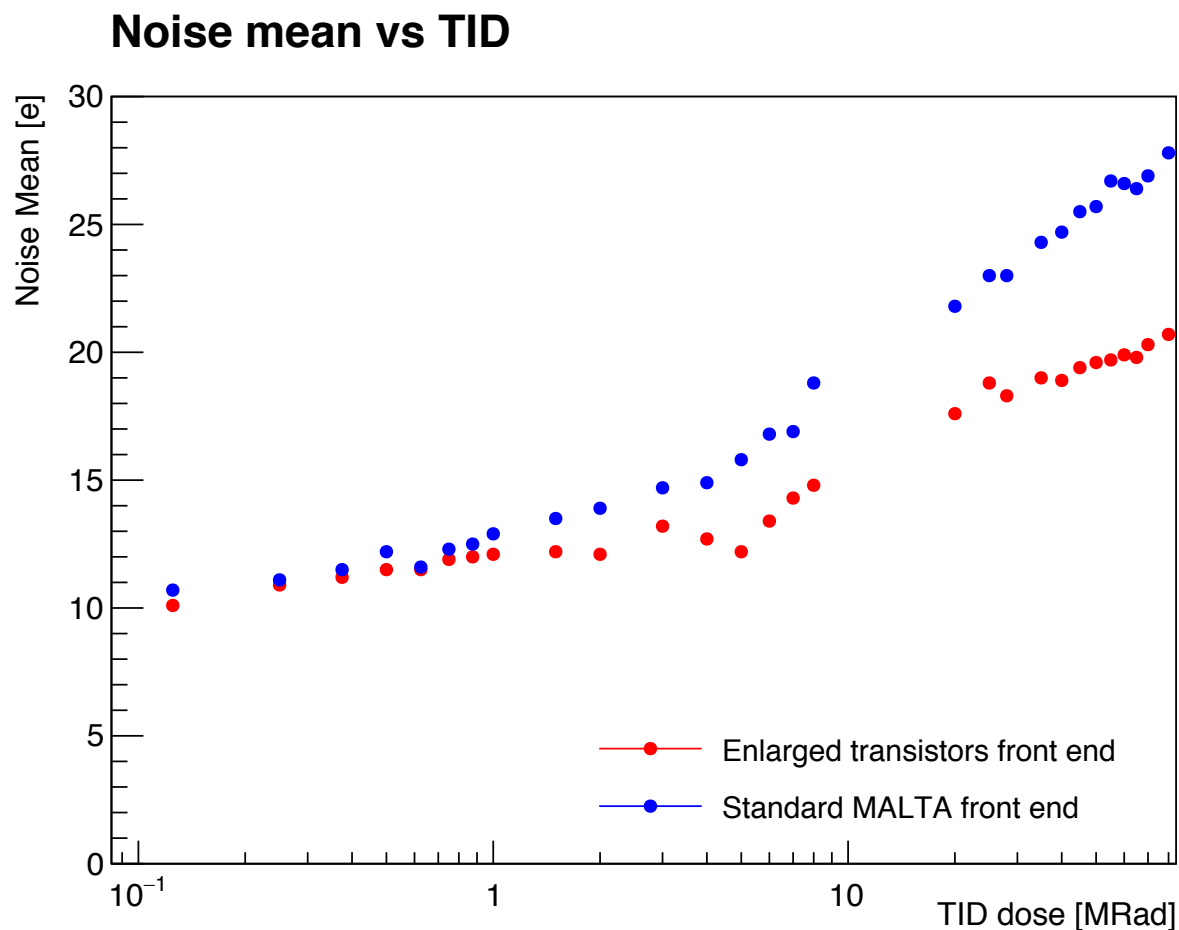
## Deep p-well + enlarged transistor



See M.  
Mironova's  
Poster

Submitted to  
arXiv:1909.08392

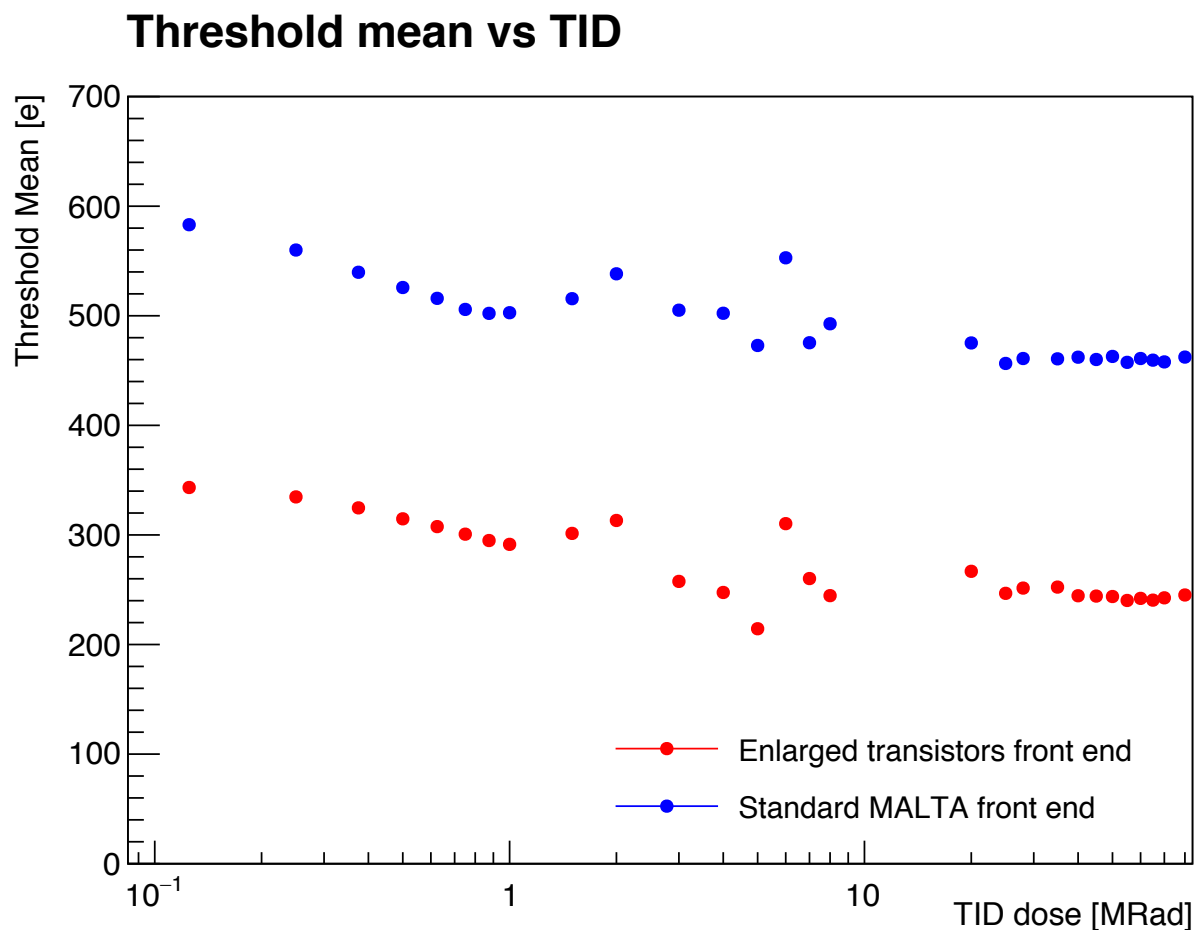
# MiniMALTA X-ray Irradiations



X-ray irradiations at Glasgow for measurement of effect of TID, esp. on front-end

- Threshold scan results
- Noise increases with TID
  - More so w/ **enlarged transistors** than **standard**

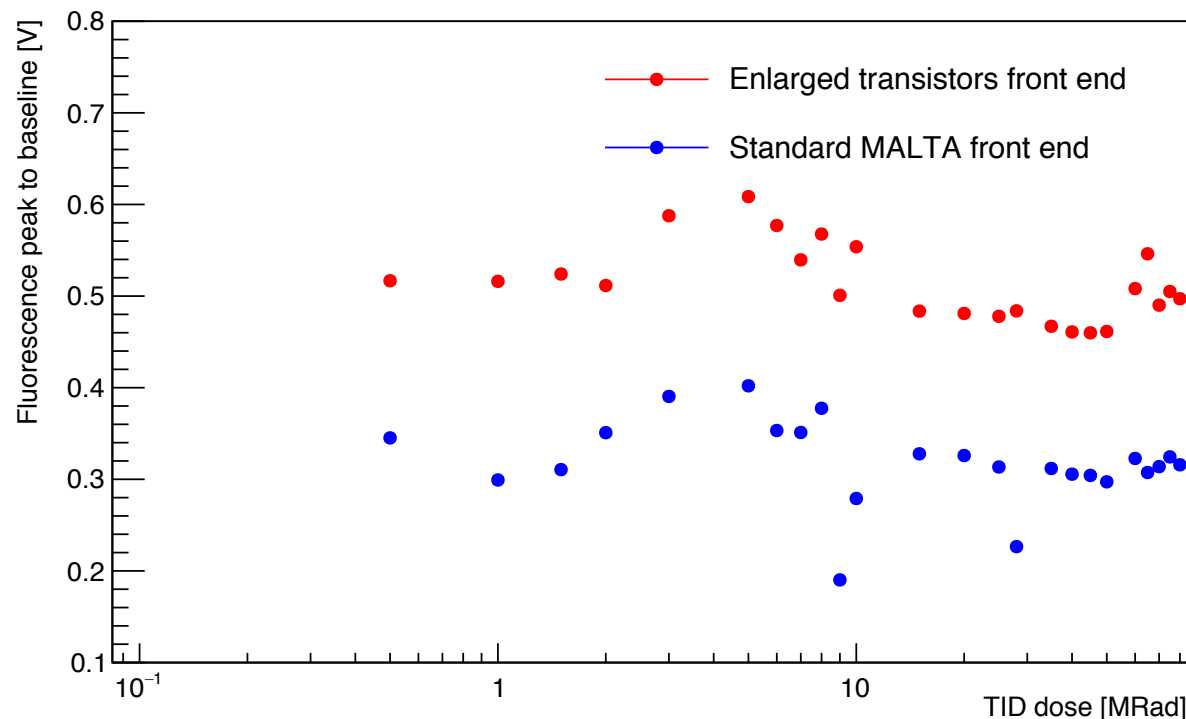
# MiniMALTA X-ray Irradiations



X-ray irradiations at Glasgow for measurement of effect of TID, esp. on front-end

- Threshold scan
- Threshold decreases after bump at 2-10 Mrad, then stabilizes
- Pixels w/ **enlarged transistors** have lower thresholds than **standard**

Amplitude of FE target as a function of TID



X-ray irradiations at Glasgow for measurement of effect of TID, esp. on front-end

- Measurements of analog pixel waveforms
- Gain increases slightly then stabilizes
- Pixels w/ **enlarged transistors** have higher gain lower thresholds than **standard**

Overall results correlate well with Diamond test beam on proton irradiated samples with TID = 70 MRad

- Additional measurements at CERN in September currently being summarized

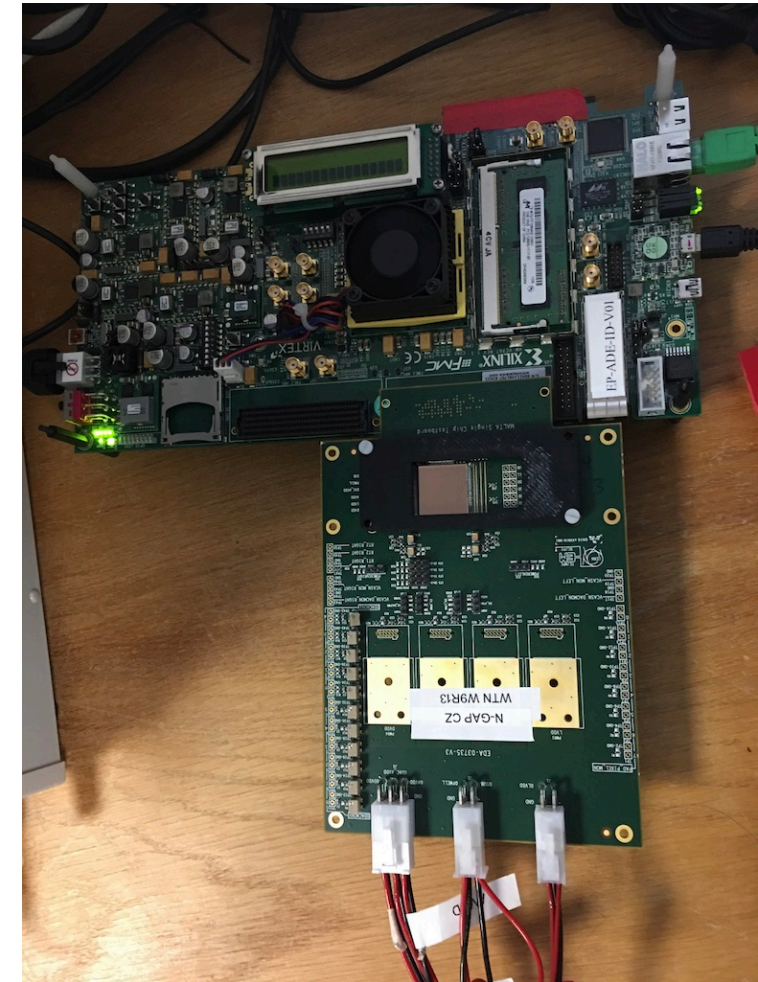
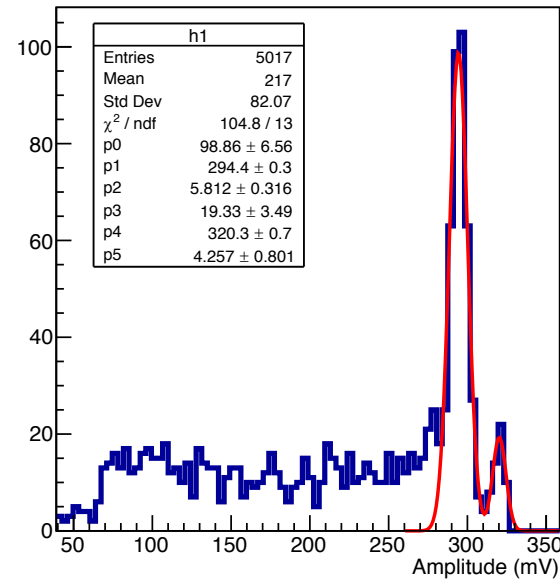
# New Sensors: MALTA SC



MALTA\_SC: Full size 2x2cm with focus on time-resolutions and radiation hardness

- Features entire wafers with substrate redesigns
- No enlarged transistor
- Also implemented on Cz Silicon
  - Lower resistivity
  - High oxygen content
  - 300  $\mu\text{m}$  substrate
  - may be able to deplete  $\sim 60 \mu\text{m}$  or more  
=> more signal
- Measurements: threshold scans, Fe55, currently testing at DESY test beam
- Neutron irradiated chips up to  $5e15$ , proton irradiations next week in Birmingham

Fe55 Spectrum



# New Sensors: MALTA V2



MALTA V2: new sensor with gain optimized FE for best time-resolution ( $\sim$ ns)

- Currently in design with focus on new FE – maximizes gain for best time-resolution (goal  $\sim$ 1ns) in small pixel matrix
- Will include all implant fixes of MiniMALTA and be produced on EPI and HR Cz material
- Submission Q4 2019



# Summary



- MALTA prototype for outer pixel layers ATLAS experiment
- TowerJazz 180 nm modified process based on ALPIDE design
- Prototype to improve radiation hardness: MiniMALTA
  - Fully efficient at  $1e15 n_{eq}/cm^2$
  - Good indications of performance at 80 Mrad
  - Design changes have intended effects
- New Cz prototypes being tested (up to  $5e15 n_{eq}/cm^2$ )
- MALTA V2 to be produced in ~Spring 2020 in epi & Cz
- A lot of work measuring new sensors to look forward to! :)



# Thank you!

W. Snoeys et al. *A process modification for CMOS monolithic active pixel sensors for enhanced depletion, timing performance and radiation tolerance*. NIMA 871 (2017) 90-96

H. Pernegger et al. *First tests of a novel radiation hard CMOS sensor process for Depleted Monolithic Active Pixel Sensors*. JINST 12 P06008 (2017)

W. Snoeys. *Monolithic CMOS sensors for high energy physics*. NIMA 924 (2019) 51–58

MiniMALTA Diamond: *Measurement of the relative response of TowerJazz Mini-MALTA CMOS prototypes at Diamond Light Source*. arXiv:1909.08392

M. Dyndal et. al. *Mini-MALTA: Radiation hard pixel designs for small-electrode monolithic CMOS sensors for the High Luminosity LHC*. arXiv:1909.11987v1

G. McGoldrick et al. *Synchronized analysis of testbeam data with the Judith software* NIMA 765 (2014) 140--145

R. M. Munker et al. *Simulations of CMOS sensors with a small collection electrode improved for a faster charge-collection and increased radiation tolerance*. 9<sup>th</sup> Workshop on Semiconductor Pixel Detectors for Particles and Imaging (PIXEL), December 2018.

A. Sharma, *Results of the Malta CMOS pixel detector prototype for the ATLAS Pixel ITK, in AIDA 2020 - Fourth Annual Meeting, Oxford, 2019*.

I. Berdalovicet al. *Monolithic pixel development in TowerJazz 180 nm CMOS for the outer pixel layers in the ATLAS experiment*. JINST 13 C01023 (2018)

P. Allport. *Applications of silicon strip and pixel-based particle tracking detectors*. [Nature Reviews Physics](#) volume 1, pages 567–576 (2019)

M. Garcia-Sciveres and N. Wermes, "A review of advances in pixel detectors for experiments with high rate and radiation", Reports on Progress in Physics, vol 81, 6, 066101, 2018.

# Backup



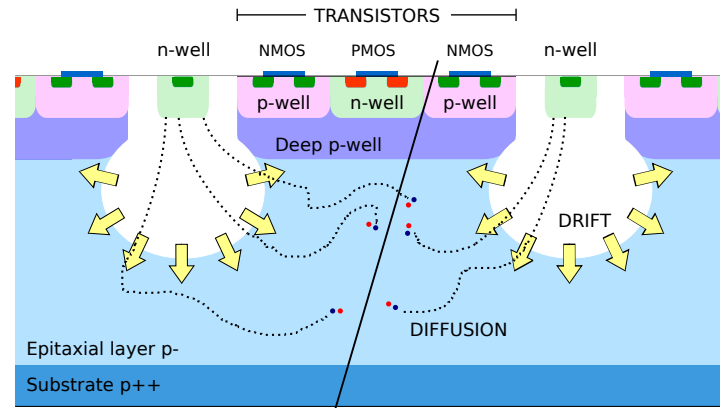
## Timeline

2017	TJ Investigator studies
Jan 2018	MALTA production
May 2018	MALTA SPS test beams MiniMALTA design submission
Nov. 2018	
January 2019	MiniMALTA production MiniMALTA irradiations & measurements
April 2019	MiniMALTA test beams
August 2019	MALTA_SC produced MALTA_SC irradiation & measurements
Now	DESY test beam for MALTA_SC & MiniMALTA

# Tower Jazz Investigator 1 & 2

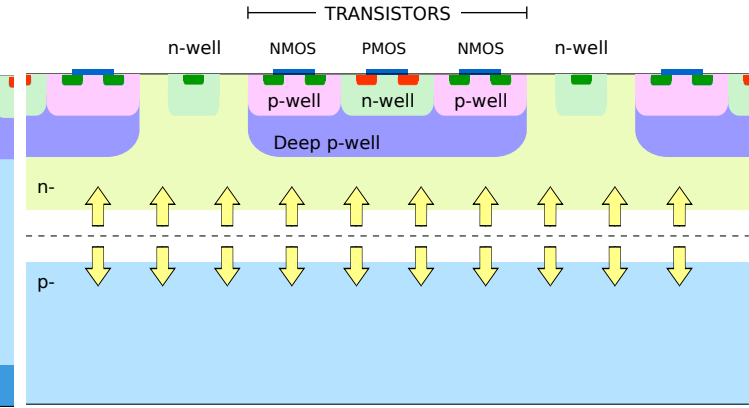


- 180 nm TJ
- Analog sensor for design optimization
- 25 -30  $\mu\text{m}$  epitaxial layer
- Small collection electrode for small ( $\sim 5\text{fF}$ ) input capacitance
- Modified process in Investigator 2 features uniform n-implant to improve lateral depletion
  - For periphery efficiency
  - Improves time walk
- Many matrices with different pixel size, electrode size, shape, etc.
- Good radiation tolerance up to  $1\text{e}15$   $n_{\text{eq}}/\text{cm}^2$  (Sr90 measurements)
- 2 chips based off Investigator: MALTA (asynchronous readout for faster data rates) and MONOPIX (synchronous readout)



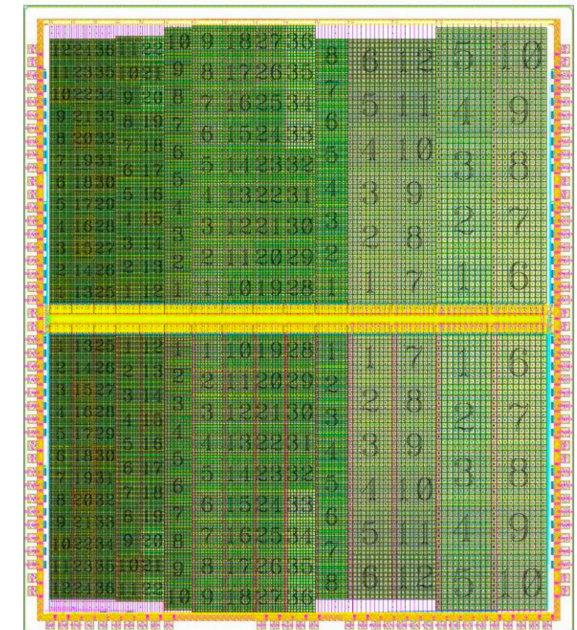
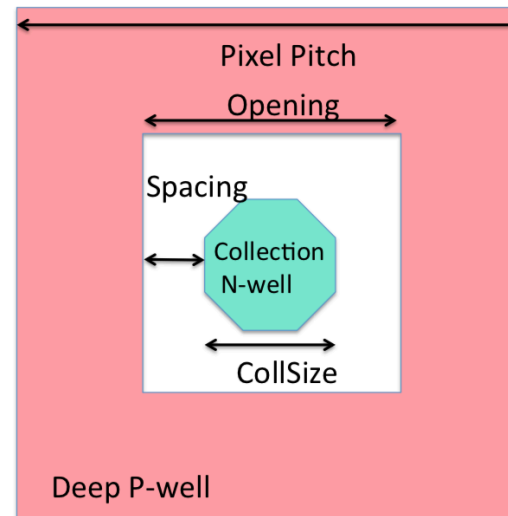
Standard Process

W. Snoeys et al. DOI 10.1016/j.nima.2017.07.046



Modified Process

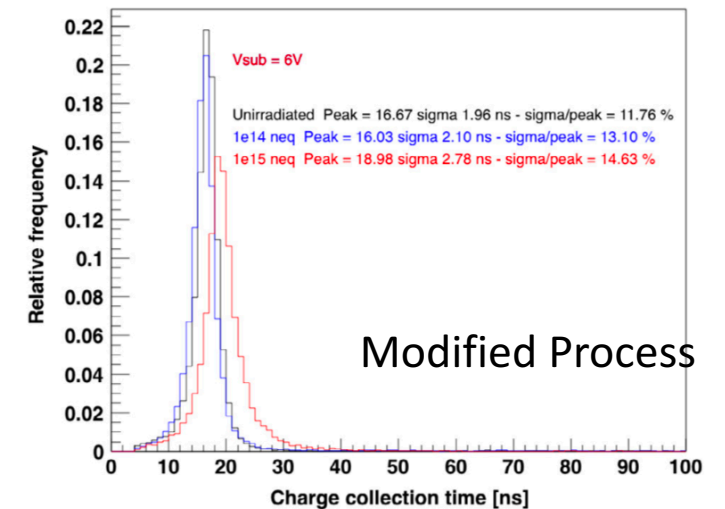
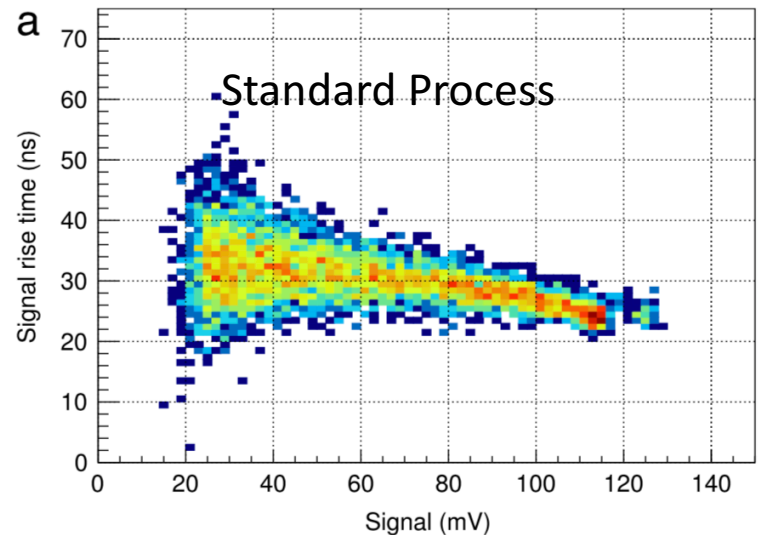
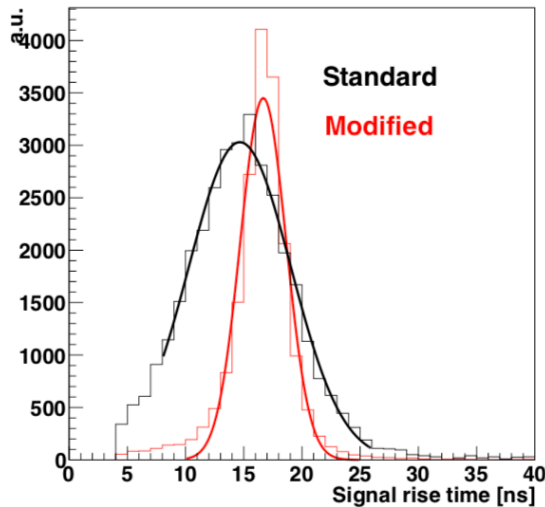
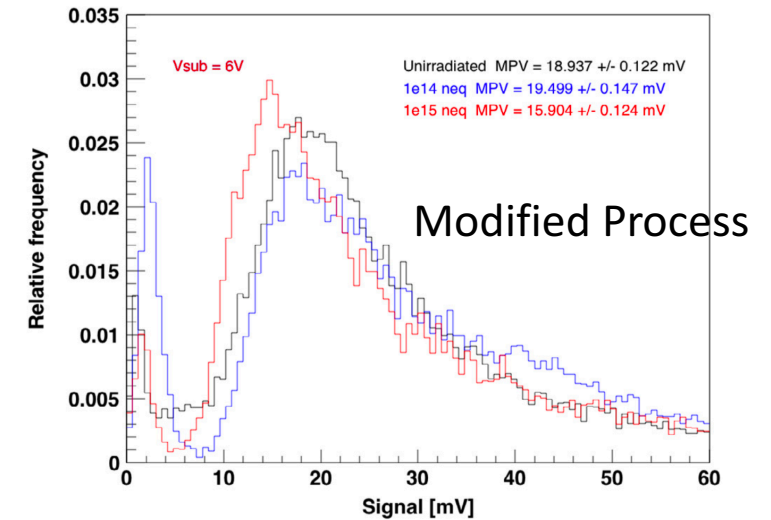
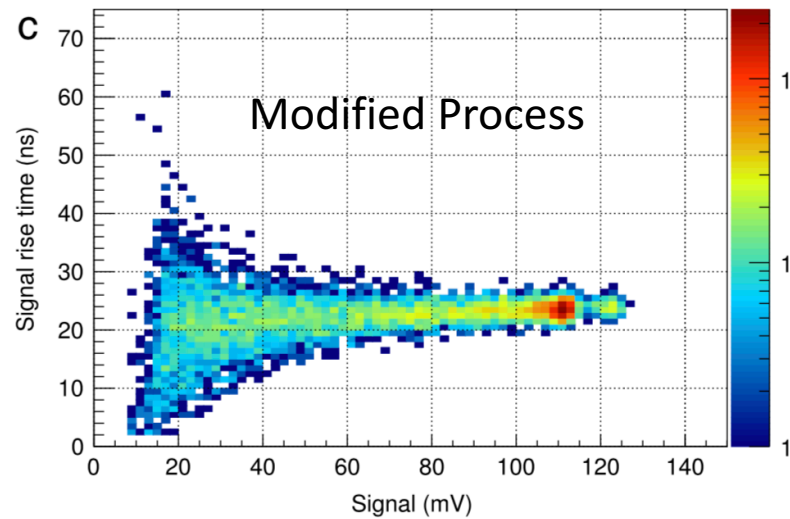
H. Pernegger et al 2017 JINST 12 P06008



# Tower Jazz Investigator



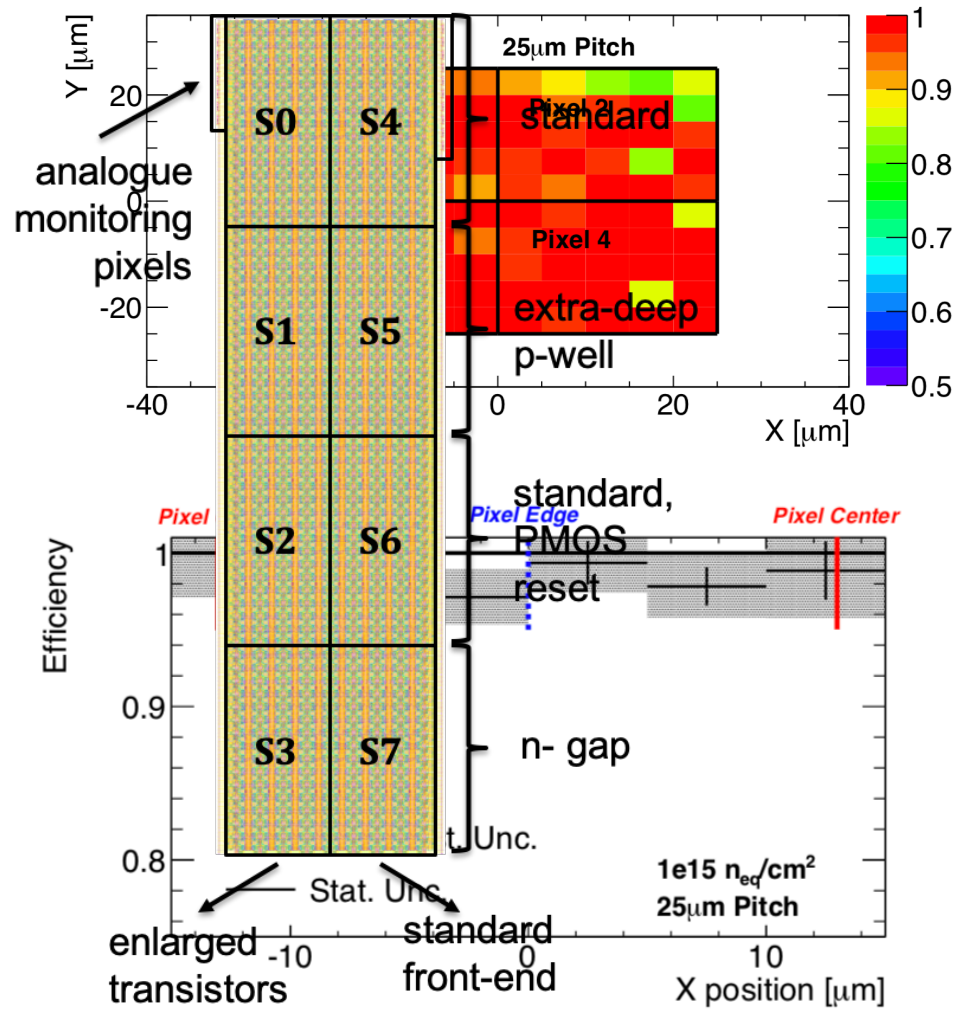
- Modified process results in faster, more uniform pulses
  - => improved time walk
- Good radiation tolerance
- Modified pixels efficient in periphery



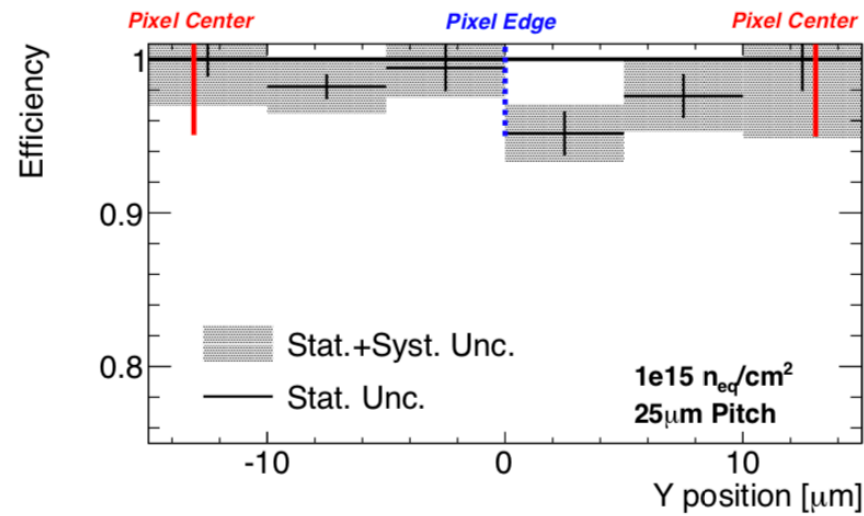
W. Snoeys et al. DOI 10.1016/j.nima.2017.07.046

H. Pernegger et al 2017 JINST 12 P06008

# Tower Jazz Investigator Efficiency



- Modified pixels efficient in periphery
- 25 um pixel w/  $1e15 n_{eq}/cm^2$
- => create chip based on modified process



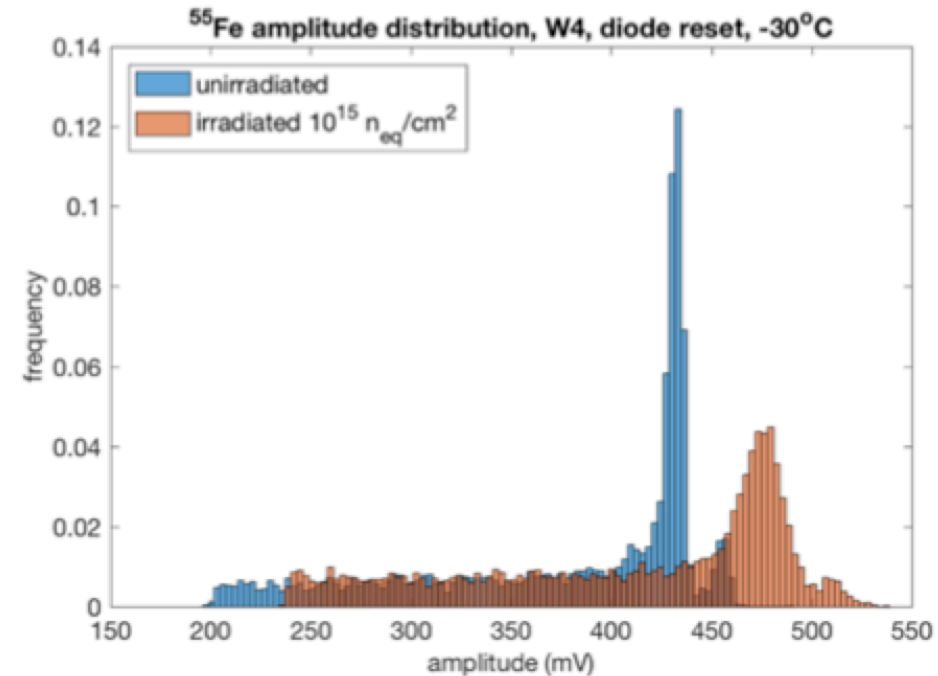
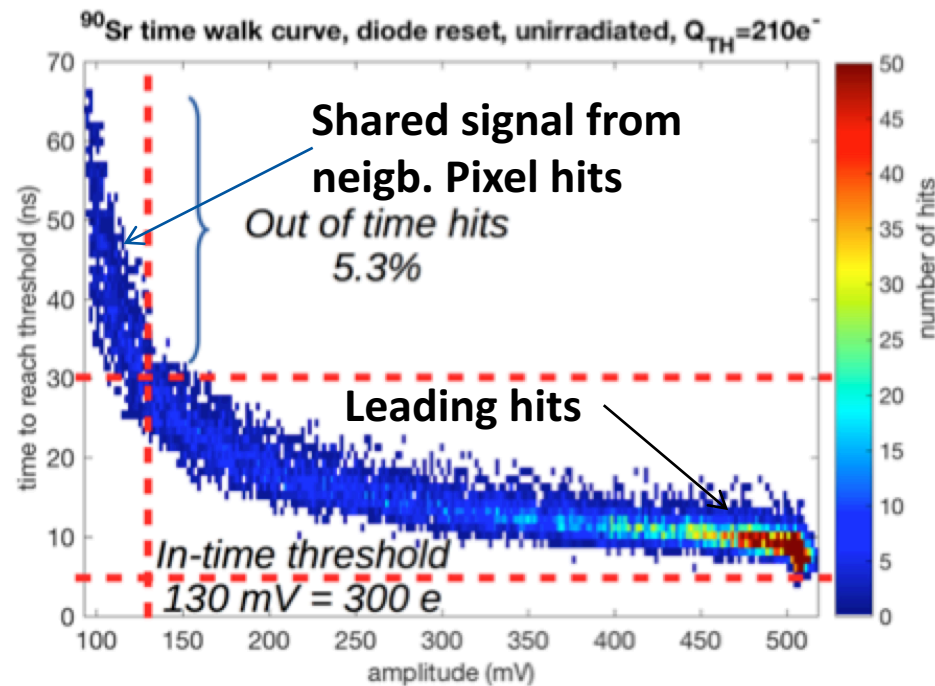
Modified Process



# MALTA analog after irradiation

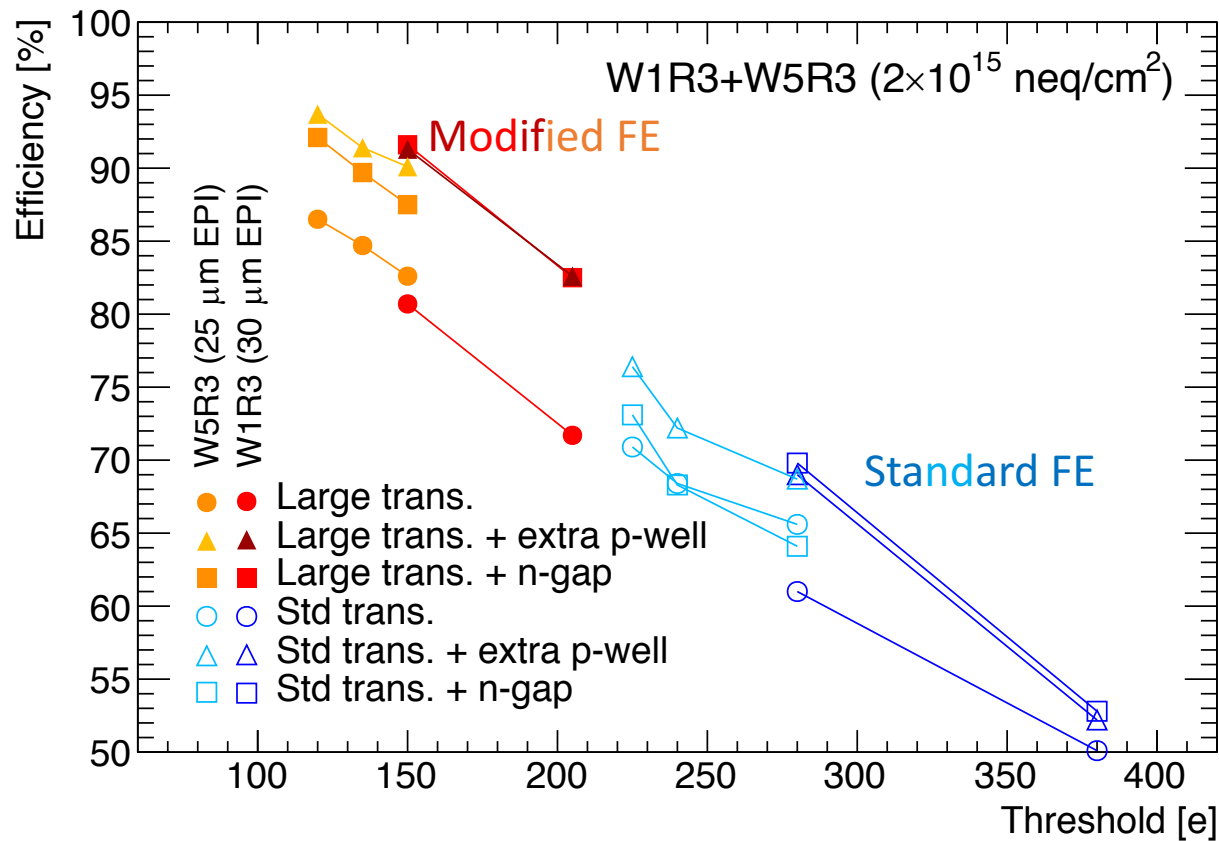


- Neutron irradiated  $n_{eq}/cm^2$
- Good analog performance for ENC and timing
- Need improvement on threshold dispersion



Copied from Heinz...

# MiniMALTA Efficiency Results



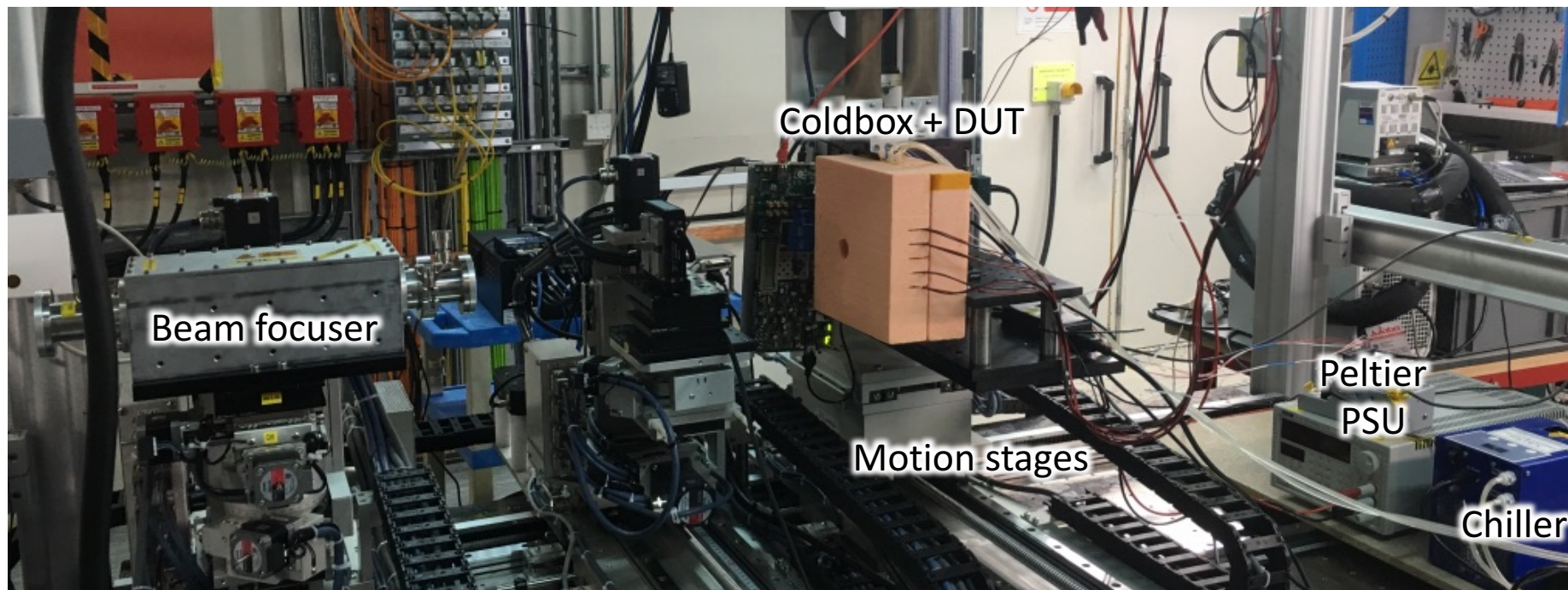
Submitted to arXiv:1909.11987v1

## Summary of $2e15$ n<sub>eq</sub>/cm<sup>2</sup> efficiencies

- Efficiency < 95 %
- One 25  $\mu$ m & one 30  $\mu$ m
- Threshold lower & efficiency higher for 30  $\mu$ m than 25  $\mu$ m epitaxial
- Efficiency seems linear w/ threshold

**Chip loses efficiency, is it still in the periphery?**

# MiniMALTA Diamond Test Beam



- April 2019 at Diamond Light Source
- Measurement of **proton** and **neutron** irradiated chips
- Focus on 3 sectors:
  - n- gap w/ enlarged transistors
  - Deep p-well w/ enlarged transistors
  - Standard MALTA (for comparison)
- Precision focused X-ray beam
  - $2 \mu\text{m}$  spot size
  - 8 keV photons
    - $\sim 2200$  e-/hole pairs
    - Slightly below mean energy deposited by MIP close to MPV
- Precision motion stages for scanning (400 nm)
- => Can make high-resolution relative response maps (basically **high precision TCT**)

# MiniMALTA Diamond Results

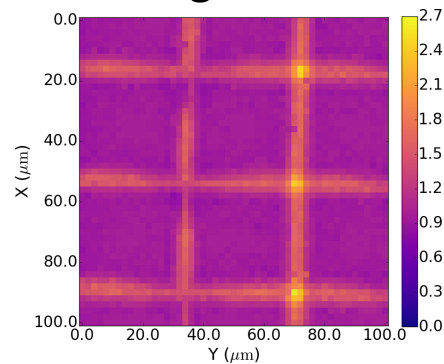
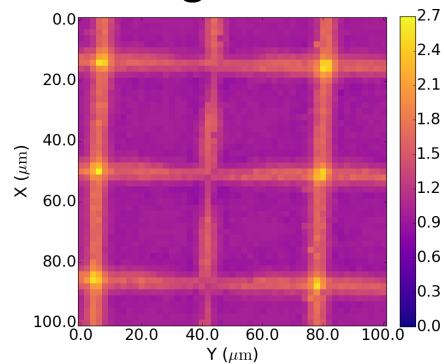
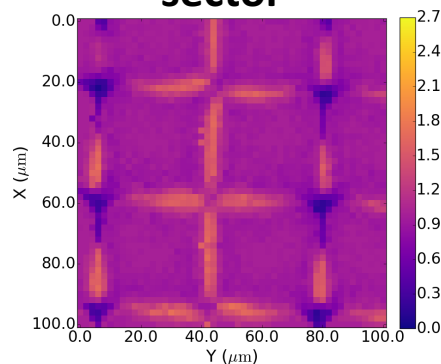


MALTA sector

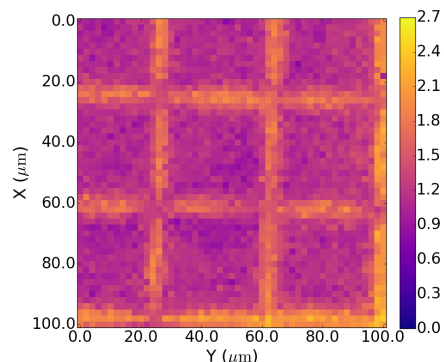
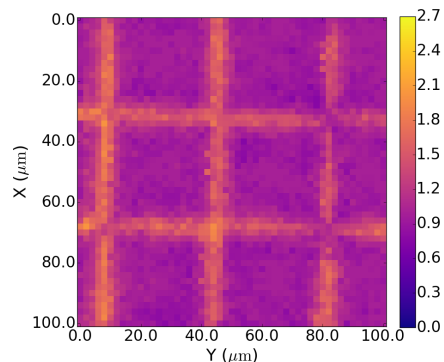
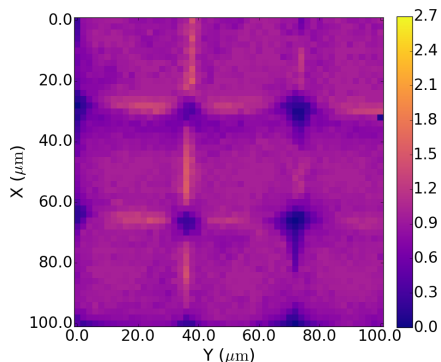
Deep p-well + enlarged transistor

n-gap + enlarged transistor

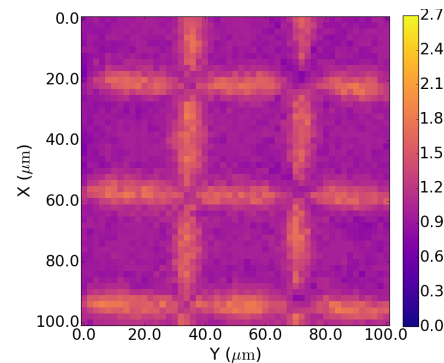
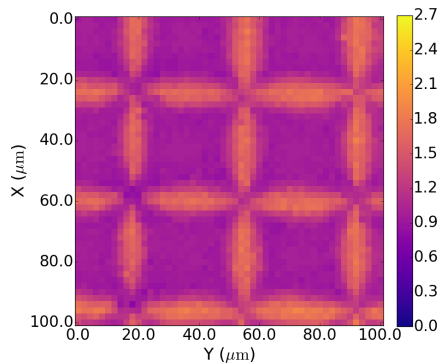
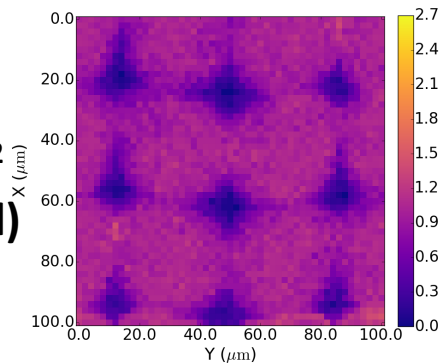
W2R11 unirradiated



W2R9 5e14 n<sub>eq</sub>/cm<sup>2</sup> 66 Mrad (proton irradi)



W2R1 1e15 n<sub>eq</sub>/cm<sup>2</sup> (neutron irradi)



- Occupancy plots from 8 keV photons
- Response in the periphery decreases w/ irradiation in the MALTA sector
- Re-designed sectors show improvement
- Charge sharing evolves with irradiation: pixels become “wider”
- Trends in integrated response match efficiency trends in ELSA
- Proton irradiated chips up to 5e14 n<sub>eq</sub>/cm<sup>2</sup> and 70 Mrad have comparable response to 1e15 n<sub>eq</sub>/cm<sup>2</sup> sensors
- More detailed results in Maria Mironova’s poster
- Can estimate MIP efficiency from results (see Maria Mironova’s poster)

